

## 1. Features and Benefits

- 3-phase BLDC gate driver
  - Level shifting between MCU PWM outputs and 3 external half-bridges
  - Compatible with 3.3V-5V microcontrollers
- Supporting different driver strength
  - MLX83203: 1.00A gate drivers
  - MLX83202: 0.33A gate drivers
- Supported supply voltage range
  - Absolute maximum rating: 45V
  - Operating range: 4.5V-28V
  - 12V-28V Battery systems
  - Automotive qualified for 12V
  - Sleep mode with current <30µA
- Two charge pump configuration modes for
  - Low voltage operation
  - Reverse polarity N-FET protection
- High-side gate drivers with bootstrap circuits
  - Integrated 12V voltage regulator
  - Supports 6x 350nC N-FETs at 20kHz PWM
  - Supports 100% PWM operation
- Integrated current sense amplifier
  - Low offset and low offset drift
  - Fast settling time < 1µs
  - Programmable gain: 8x-48x
- Extensive diagnostics
  - Under/over voltage detection
  - Over temperature warning
  - Programmable V<sub>DS</sub> monitoring
  - V<sub>GS</sub> monitoring
- Serial, PWM diagnostics interface
  - Configurable diagnostics
  - Full diagnostic feedback
- Customer configurable EEPROM
  - Driver configuration
  - Diagnostics configuration
- Small package
  - 32-pin QFN-EP
  - Wettable flanks
- AEC-Q100 qualified

## 2. Application Examples

- Automotive 12V BLDC applications
  - Water pump / Oil pump / Fuel pump
  - Engine Cooling fan
  - HVAC blower / compressor
- Industrial BLDC motor drivers up to 28V
  - Pumps
  - Fans
  - Blowers / compressors

## 3. Ordering Information

Product	Temperature	Package	Option Code	Packing Form
MLX83203	K (-40°C to 125°C)	LW (QFN32-EP 5x5mm wettable flanks)	DDA-000	RE (Reel)
MLX83202	K (-40°C to 125°C)	LW (QFN32-EP 5x5mm wettable flanks)	DDA-000	RE (Reel)

Ordering Example: “MLX83203KLW-DDA-000-RE”.

## 4. Functional Diagram

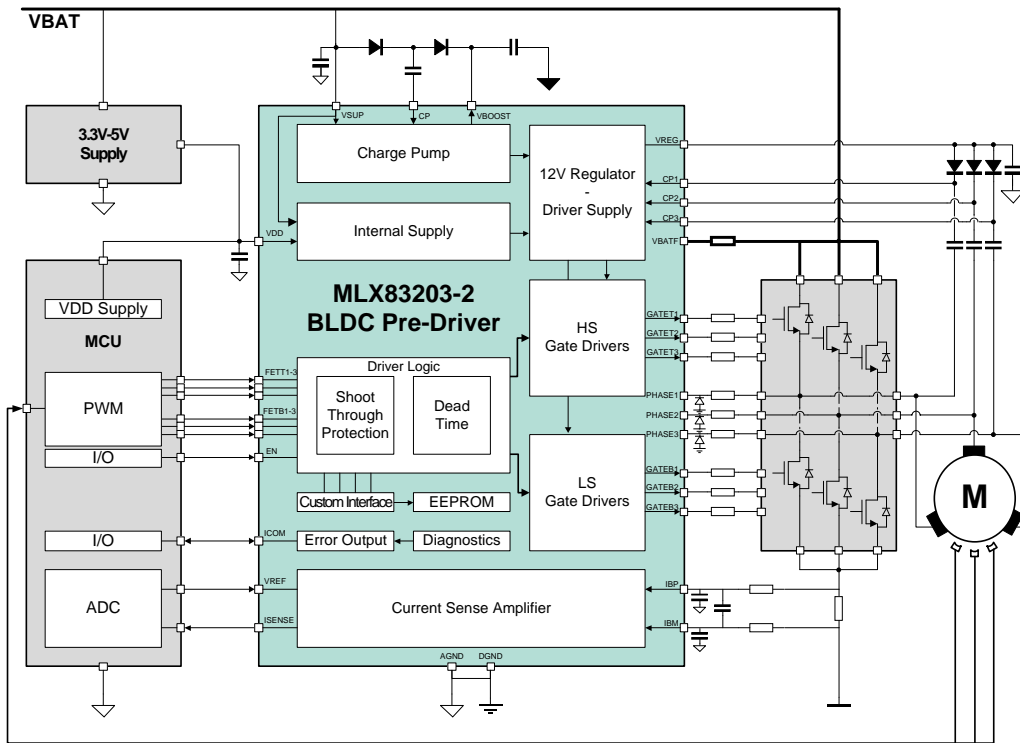


Figure 4-1 Typical application diagram

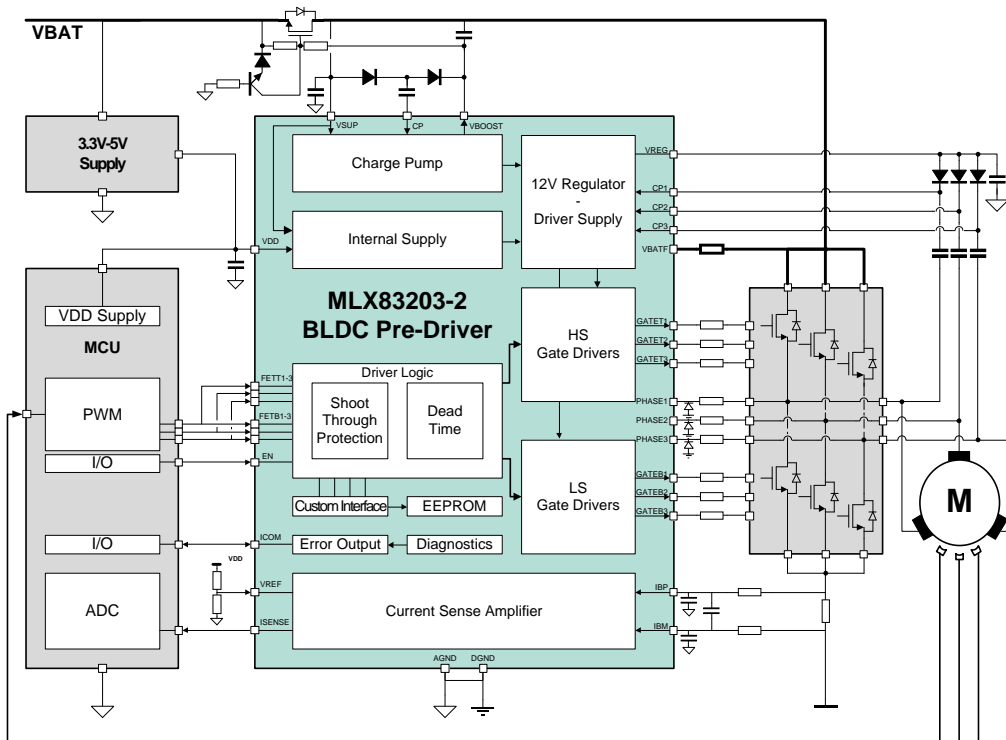


Figure 4-2 Alternative application diagram with reverse polarity N-FET

## 5. General Description

The MLX83203-2 is a three phase pre-driver (also called ‘bridge’ or ‘gate’ driver) IC with integrated current sense amplifier. This device is used to drive brushless DC motors in combination with a microcontroller and six discrete power N-FETs.

For the high power applications, the MLX83203 provides powerful gate drivers of 1A typical. The MLX83202 has reduced gate drive strength of 300mA and targets mid power applications.

Both devices are able to control six external N-FETs in the supply range from 4.5V to 28V, by means of the integrated charge pump. The high side gate drivers are supplied via bootstrap circuits. The trickle charge pump allows 100% PWM operation despite the use of bootstrap capacitors. The bootstrap voltage regulator is optimized for gate charges up to 350nC per FET at 20 kHz PWM.

The device comprises various monitoring and protection functions, including under voltage and over voltage detection at multiple internal voltage nodes, over temperature detection, drain-source and gate-source voltage monitoring of the external N-FETs. In case of fault detection, the ICOM diagnostics interface will inform the microcontroller with a PWM signal, whose duty cycle indicates the nature of the error.

An integrated fast, high-bandwidth, low offset current sense amplifier allows for precise torque control, with programmable gain selection.

The MLX83203-2 provides an EEPROM for configurability, avoiding the need for a high pin-count package. The configuration allows the customer to optimize the pre-driver’s operation for different applications.

## 6. Contents

<b>1. Features and Benefits</b> .....	<b>1</b>
<b>2. Application Examples</b> .....	<b>1</b>
<b>3. Ordering Information</b> .....	<b>1</b>
<b>4. Functional Diagram</b> .....	<b>2</b>
<b>5. General Description</b> .....	<b>3</b>
<b>6. Contents</b> .....	<b>4</b>
<b>7. Pin Configuration &amp; Definition</b> .....	<b>5</b>
7.1. Pin Configuration .....	5
7.2. Pin Definition.....	5
<b>8. Absolute Maximum Ratings</b> .....	<b>7</b>
<b>9. Operating Range</b> .....	<b>7</b>
<b>10. General Electrical Specifications</b> .....	<b>8</b>
10.1. MLX83203 Typical Performance Graphs .....	15
10.2. MLX83202 Typical Performance Graphs .....	16
<b>11. Block Diagram</b> .....	<b>18</b>
<b>12. Functional Description</b> .....	<b>19</b>
12.1. Supply System .....	19
12.2. Gate Drivers .....	23
12.3. Integrated Current Sense Amplifier .....	24
12.4. Protection and Diagnostic Functions.....	25
12.5. EEPROM Configuration.....	30
<b>13. ESD Protection</b> .....	<b>37</b>
<b>14. Package Information</b> .....	<b>38</b>
14.1. Package Marking.....	38
14.2. Package Data.....	39
<b>15. Revision History</b> .....	<b>40</b>
<b>16. Standard Information</b> .....	<b>42</b>
<b>17. ESD Precautions</b> .....	<b>42</b>
<b>18. Contact</b> .....	<b>43</b>
<b>19. Disclaimer</b> .....	<b>43</b>

## 7. Pin Configuration & Definition

### 7.1. Pin Configuration

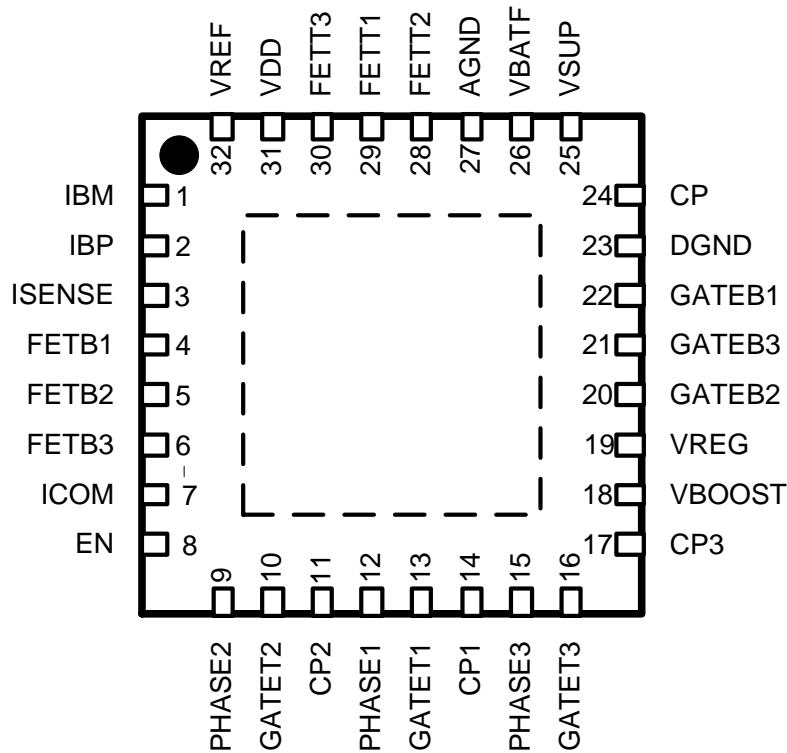


Figure 7-1 Pin configuration

### 7.2. Pin Definition

Pin #	Name	Description
1	IBM	Current sense amplifier negative input
2	IBP	Current sense amplifier positive input
3	ISENSE	Current sense amplifier output
4	FETB1	Low-side FET1 PWM control input (active low) MISO output for SPI
5	FETB2	Low-side FET2 PWM control input (active low) CLK input for SPI
6	FETB3	Low-side FET3 PWM control input (active low) MOSI input for SPI
7	ICOM	Bidirectional, serial diagnostics interface CSB input for SPI
8	EN	Enable input for gate driver outputs (active high)
9	PHASE2	Motor phase 2
10	GATET2	High-side FET2 gate driver output

## Datasheet

11	CP2	High-side FET2 bootstrap capacitor
12	PHASE1	Motor phase 1
13	GATET1	High-side FET1 gate driver output
14	CP1	High-side FET1 bootstrap capacitor
15	PHASE3	Motor phase 3
16	GATET3	High-side FET3 gate driver output
17	CP3	High-side FET3 bootstrap capacitor
18	VBOOST	Charge pump boosted supply output
19	VREG	Driver supply output for bootstrap capacitors
20	GATEB2	Low-side FET2 gate driver output
21	GATEB3	Low-side FET3 gate driver output
22	GATEB1	Low-side FET1 gate driver output
23	DGND	Driver ground
24	CP	Charge pump floating capacitor
25	VSUP	Power supply input (Battery input)
26	VBATF	Battery voltage connection for VDS-monitoring
27	AGND	Analog ground
28	FETT2	High-side FET2 PWM control input (active high)
29	FETT1	High-side FET1 PWM control input (active high)
30	FETT3	High-side FET3 PWM control input (active high)
31	VDD	Digital supply for IO's and current sense amplifier
32	VREF	Current sense amplifier reference input
33	PAD	Exposed pad

*Table 7-1 Pin definition*

## 8. Absolute Maximum Ratings

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Power supply voltage	$V_{VSUP}, V_{BATF}$	-0.3	-	45	V	$t < 500\text{ms}$ (during load dump)
Power supply voltage	$V_{VSUP}, V_{BATF}$	-0.3	-	28	V	Permanent (functional)
VBATF voltage	$V_{BATF}$	-0.3	-	$V_{SUP}+1.4$	V	For any IC-version before DDA
Negative input current	$I_{VSUP}$	-15	-	-	mA	
Negative input current	$I_{VBATF}$	-10	-	-	mA	Defines with max. reverse polarity voltage the $R_{VBATF}$
Digital supply voltage	$V_{VDD}$	-0.3	-	5.5	V	
Analog input voltage	$V_{VREF}, V_{IBM}, V_{IBF}$	-0.3	-	$V_{DD}+0.3$	V	
Analog output voltage	$V_{ISENSE}$	-0.3	-	$V_{DD}+0.3$	V	
Digital input voltage	$V_{FETBx}, V_{FETT_x}, V_{EN}$	-0.3	-	$V_{DD}+0.3$	V	
Digital input current		-10	-	10	mA	
Digital output voltage	$V_{ICOM}$	-0.3	-	$V_{DD}+0.3$	V	
Output voltage	$V_{GATEBx}, V_{REG}$	-0.3	-	17	V	
Output voltage	$V_{GATEx}$	-0.3	-	$V_{REG}+35$	V	
Input voltage on CPx pins	$V_{CPx}$	-0.3	-	$V_{REG}+35$	V	
Input voltage on PHASEx pins	$V_{PHASEx}$	-0.7	-	45	V	
Maximum latch-up free current at any pin	$I_{LATCH}$	-100	-	100	mA	According to JEDEC JESD78, AEC-Q100-004
ESD capability	ESD	-2	-	+2	kV	Human Body Model
Storage temperature	$T_{stg}$	-55	-	150	°C	
Junction temperature	$T_J$	-40	-	150	°C	
Thermal resistance SOIC-16	$R_{th-JA}$	-	37	-	K/W	In free air on multilayer PCB (JEDEC 1s2p)
Thermal resistance SOIC-16	$R_{th-JC}$	-	10	-	K/W	Referring center of exposed pac

Table 8-1 Absolute maximum ratings

Exceeding the absolute maximum ratings may cause permanent damage. Exposure to absolute maximum-rated conditions for extended periods may affect device reliability.

## 9. Operating Range

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Power supply voltage range	$V_{VSUP}$	4.5	-	28	V	Full functionality
Digital supply voltage range	$V_{VDD}$	3	-	5.5	V	CP discharged, power FETs off
Ambient temperature	$T_A$	-40	-	125	°C	
Junction temperature	$T_J$	-40	-	150	°C	

Table 9-1 Operating range

## 10. General Electrical Specifications

	Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
	<b>Power Supply VSUP</b>						
No.1	Supply voltage range	V <sub>SUP</sub>	Functional	7	-	18	V
No.2	Supply voltage extended range low	V <sub>SUP_ERL</sub>	Functional w. decreased gate drive voltage	4.5	-	7	V
No.3	Supply voltage extended range high	V <sub>SUP_ERH</sub>		18	-	28	V
No.4	Quiescent current from V <sub>SUP</sub>	I <sub>SUP_SLEEP</sub>	V <sub>DD</sub> = Low	-	-	30	µA
No.5	Operating current from V <sub>SUP</sub>	I <sub>SUP_INT</sub>	Pre-driver operation 25kHz PWM, no load	-	-	5	mA
No.6	Supply over voltage high	V <sub>SUP_OVH</sub>	Warning on ICOM	-	-	35	V
No.7	Supply over voltage low	V <sub>SUP_OVL</sub>	ICOM released	30	-	-	V
No.8	Supply over voltage hysteresis	V <sub>SUP_OVHY</sub>		0.4	-	1	V
No.9	Supply over voltage debounce time	V <sub>SUP_OV_DEB</sub>		-	-	2	µs
No.10	Supply under voltage high	V <sub>SUP_UVH</sub>	ICOM released	-	-	6	V
No.11	Supply under voltage low	V <sub>SUP_UVL</sub>	Warning on ICOM	5	-	-	V
No.12	Supply under voltage hysteresis	V <sub>SUP_UVHY</sub>		0.2	-	0.5	V
No.13	Supply under voltage debounce time	V <sub>SUP_UV_DEB</sub>		-	-	10	µs
No.14	Power on reset level	V <sub>POR</sub>	Reset released on rising edge V <sub>SUP</sub> when V <sub>DD</sub> =high	2.6	-	4.5	V
	<b>VVBATF</b>						
No.15	Leakage from V <sub>BATF</sub> to GND	R <sub>VBATF_LEAK</sub>	Pre-driver not in sleep	-	-	30	µA
	<b>Temperature Warning</b>						
No.16	Over temperature high	OVT <sub>H</sub>	Warning on ICOM	-	185	-	°C
No.17	Over temperature low	OVT <sub>L</sub>	ICOM released	-	168	-	°C
	<b>On-Chip Oscillator</b>						
No.18	Oscillator frequency	f <sub>OSC</sub>	Internal Oscillator	6.8	8	9.2	MHz



## Datasheet

		<u>Charge Pump CP, VBOOST</u>					
No.19	Output slew rate	$V_{CP}$		-	100	-	V/ $\mu$ s
No.20	Charge pump frequency	$f_{CP}$		170	200	230	kHz
No.21	Reverse polarity N-FET gate-source voltage ( $V_{BOOST}-V_{SUP}$ )	$V_{GS\_RPFET}$	<ul style="list-style-type: none"> <li>CP Mode 1</li> <li><math>V_{SUP} &gt; 7V</math></li> <li><math>I_{REG} &lt; 20mA</math></li> </ul>	5	12	13	V
No.22	Resistive load from $V_{BOOST}$ to GND	$R_{BOOST\_LEAK}$	<ul style="list-style-type: none"> <li><math>R_{Typ}</math> at room temperature</li> <li><math>R_{Min}</math> at 150°C <math>T_J</math></li> <li>(excl. <math>R_{VREG\_LEAK}</math>)</li> </ul>	6	8	-	M $\Omega$ m
No.23	$V_{BOOST}$ under voltage high	$V_{BOOST\_UVH}$	COM released <ul style="list-style-type: none"> <li>CP Mode 0 (<math>V_{BOOST}</math>)</li> <li>CP Mode 1 (<math>V_{BOOST}-V_{SUP}</math>)</li> </ul>	6.1	-	7.2	V
No.24	$V_{BOOST}$ under voltage low	$V_{BOOST\_UVL}$	Warning on ICOM <ul style="list-style-type: none"> <li>CP Mode 0 (<math>V_{BOOST}</math>)</li> <li>CP Mode 1 (<math>V_{BOOST}-V_{SUP}</math>)</li> </ul>	5.6	-	6.7	V
No.25	$V_{BOOST}$ discharge stop	$V_{BOOST\_DISSTOP}$	<ul style="list-style-type: none"> <li>CP Mode 1 (<math>V_{BOOST}-V_{SUP}</math>)</li> <li>Discharge activated by <math>V_{SUP\_OV}</math> and topped by <math>V_{BOOST\_DIS\_STOP}</math></li> </ul>	$V_{SUP}-0.2$	-	$V_{SUP}+0.8$	V
No.26	$V_{BOOST}$ discharge current	$I_{BOOST\_DIS}$	<ul style="list-style-type: none"> <li>CP Mode 1 (<math>V_{BOOST}-V_{SUP}</math>)</li> <li>From <math>V_{BOOST}</math> to DGND</li> </ul>	25	-	90	mA
		<u>Driver Supply VREG</u>					
No.27	Load current on $V_{REG}$	$I_{REG\_CPMODE0}$	<ul style="list-style-type: none"> <li><math>V_{REG} &gt; 11V</math></li> <li>CP Mode 0, <math>EN\_CP = 1</math></li> </ul>	-	-	40	mA
		$I_{REG\_CPMODE1}$	<ul style="list-style-type: none"> <li><math>V_{REG} &gt; 11V</math></li> <li>CP Mode 1, <math>EN\_CP = 1</math></li> </ul>	-	-	20	mA
No.28	Output voltage $V_{REG}$	$V_{REG}$	<ul style="list-style-type: none"> <li>CP Mode 0, <math>EN\_CP = 1</math></li> <li><math>V_{SUP} &gt; 8V</math></li> <li><math>I_{REG} &lt; 40mA</math></li> </ul>	11	12	13	V
			<ul style="list-style-type: none"> <li>CP Mode 0, <math>EN\_CP = 1</math></li> <li><math>7V &lt; V_{SUP} &lt; 8V</math></li> <li><math>I_{REG} &lt; 40mA</math></li> </ul>	10	-	13	V
		$V_{REG}$	<ul style="list-style-type: none"> <li>CP Mode 1, <math>EN\_CP = 1</math></li> <li><math>I_{REG} &lt; 20mA</math></li> </ul>	11	12	13	V
No.29	Internal resistive load from $V_{REG}$ to GND	$R_{VREG\_LEAK}$	<ul style="list-style-type: none"> <li><math>R_{Typ}</math> at room temperature</li> <li><math>R_{Min}</math> at 150°C <math>T_J</math></li> </ul>	0.3	0.4	-	M $\Omega$ m
No.30	$V_{REG}$ over voltage high	$V_{REG\_OVH}$	Warning on ICOM	14.2	-	16.5	V

## Datasheet

No.31	V <sub>REG</sub> over voltage low	V <sub>REG_OVL</sub>	▫ ICOM released	13.5	-	15.8	V
No.32	V <sub>REG</sub> over voltage hysteresis	V <sub>REG_OVHY</sub>		0.65	-	1.5	V
No.33	V <sub>REG</sub> under voltage high	V <sub>REG_UVH</sub>	▫ ICOM released	7.2	-	8.1	V
No.34	V <sub>REG</sub> under voltage low	V <sub>REG_UVL</sub>	▫ Warning on ICOM	6.9	-	7.8	V
No.35	V <sub>REG</sub> under voltage hysteresis	V <sub>REG_UVHY</sub>		0.3	-	0.7	V
<u>Digital Supply VDD</u>							
No.36	V <sub>DD</sub> operating current	I <sub>DD</sub>	▫ Incl. ICOM current sourcing	4	-	7	mA
No.37	V <sub>DD</sub> pull down resistance	V <sub>DD_RPD</sub>		200	300	370	kΩm
No.38	V <sub>DD</sub> input voltage	V <sub>DD</sub>	▫ V <sub>DD</sub> = 3.3V or 5V	3	-	5.5	V
No.39	V <sub>DD</sub> under voltage high	V <sub>DD_UVH</sub>	▫ ICOM released	2.55	-	2.95	V
No.40	V <sub>DD</sub> under voltage low	V <sub>DD_UVL</sub>	▫ Warning on ICOM	2.45	-	2.85	V
No.41	V <sub>DD</sub> under voltage hysteresis	V <sub>DD_UVHY</sub>		0.08	0.10	0.14	V
No.42	V <sub>DD</sub> sleep voltage high	V <sub>DD_SLEEPH</sub>	▫ Out of sleep	2.1	-	2.7	V
No.43	V <sub>DD</sub> sleep voltage low	V <sub>DD_SLEEPL</sub>	▫ Go to sleep	1.6	-	2.1	V
No.44	V <sub>DD</sub> sleep voltage hysteresis	V <sub>DD_SLEEPHY</sub>		0.45	0.58	0.80	V

## Datasheet

Gate Drivers							
No.45	Rise time	$t_r$	▪ $C_{LOAD} = 1nF$ , 20% to 80%	6	7	15	ns
No.46	Fall time	$t_f$	▪ $C_{LOAD} = 1nF$ , 80% to 20%	4	7	15	ns
No.47	Pull-up ON resistance low-side pre-driver	$R_{ON\_UP}$	▪ $V_{SUP} > 7V$ ▪ -10mA, $T_J = -40^\circ C$	24 (10)	-	7.0 (30)	Ωm
	Pull-up ON resistance high-side pre-driver		▪ -10mA, $T_J = 150^\circ C$ ▪ (for MLX83202)	2.0 (15)	-	9.2 (30)	Ωm
No.48	Pull-down ON resistance low-side pre-driver	$R_{ON\_DN}$	▪ $V_{SUP} > 7V$ ▪ 10mA, $T_J = -40^\circ C$	15 (10)	-	5.7 (30)	Ωm
	Pull-down ON resistance high-side pre-driver		▪ 10mA, $T_J = 150^\circ C$ ▪ (for MLX83202)	2.0 (15)	-	9.2 (30)	Ωm
No.49	Turn-on gate drive peak current (sourcing)	$I_{GON}$	▪ $V_{GS} = 0V$ , $V_{SUP} > 7V$ ▪ (for MLX83202)		-	-1.4 (-0.45)	A
No.50	Turn-off gate drive peak current (sinking)	$I_{GOFF}$	▪ $V_{GS} = 12V$ , $V_{SUP} > 7V$ ▪ (for MLX83202)		-	1.6 (0.45)	A
No.51	Propagation delay	$t_{PDDRV}$	▪ From logic input threshold to 2V $V_{GS}$ drive output at no load	20	-	120 <sup>1</sup>	ns
No.52	Propagation delay matching	$t_{PDDRM}$	▪ Transitions at the different phases at no load condition	-20	-	20	ns
No.53	Programmable dead time : asynchronous internal delay between high-side and low-side pre-driver of one half bridge	$t_{DEAD}$	▪ DEAD_TIME [ 2:0] =	000		0.00	
			001		0.51		
			010		0.80		
			011	-25%	1.10	+25%	
			100		1.67		
			101		2.30		
			110		3.40		
			111		6.90		
No.54	Dead time matching between different channels	$t_{DEAD\_TOL}$		-15	-	15	%
No.55	Programmable drain-source voltage for monitoring of external N-FETs	$V_{VDS\_MON}$	▪ VDSMON[2:0] =	000		Disabled	
			001	0.40	0.50	0.60	
			010	0.60	0.75	0.90	
			011	0.85	1.00	1.15	
			100	1.05	1.25	1.45	
			101	1.25	1.50	1.75	
			110	1.50	1.75	2.00	

<sup>1</sup> For bare it is specified to 200ns max due measurement accuracy at wafer level

## Datasheet

				111	170	200	230		
No.56	Programmable drain-source monitor blanking time: Delay between gate high and enabling corresponding $V_{DS}$ monitor	$t_{VDS\_BL}$	$/DS\_BLANK\_TIME[1:0] = 00$ $01$ $10$ $11$	5.10 2.55 1.28 0.60	6.80 3.40 1.70 0.80	8.50 4.25 2.13 1.00			$\mu s$
No.57	Sleep gate discharge resistor	Rsgd	<ul style="list-style-type: none"> <li>Internal resistance between FET gate-source pins to switch-off FET. <math>V_{DD} = 0V</math> (sleep mode)</li> <li><math>V_{GS} = 0.5V</math></li> </ul>	-	-	1			k $\Omega$ m
No.58	Trickle charge pump current capability	$I_{TCP}$	<ul style="list-style-type: none"> <li><math>V_{SUP} &gt; 12V</math></li> <li>PHASEx = <math>V_{SUP}</math></li> <li><math>V_{GSx} = V_{PHASEx} + 6.5V</math></li> <li><math>I_{TCP,max}</math> @ <math>T_J = 150C</math></li> <li>See performance graphs</li> </ul>	-	-	-25 -20 ( $T_J > 150C$ )			$\mu A$
No.59	$V_{GS}$ under voltage threshold high	$V_{GS\_UVH}$	<ul style="list-style-type: none"> <li>ICOM released</li> </ul>	42	-	70			% $V_{REG}$
No.60	$V_{GS}$ under voltage threshold low	$V_{GS\_UVL}$	<ul style="list-style-type: none"> <li>Warning on ICOM</li> </ul>	36	-	63			% $V_{REG}$
No.61	PWM frequency	$f_{DR\_PWM}$		-	20	100			k $Hz$
No.62	Leakage from CPx - PHASEx	$R_{CP\_LEAK}$	<ul style="list-style-type: none"> <li><math>R_{Typ}</math> at room temperature</li> <li><math>R_{Min}</math> at <math>150^\circ C</math> <math>T_J</math></li> </ul>	0.5	1	-			M $\Omega$ m
No.63	$V_{CPx}$ discharge current	$I_{BOOST\_DIS}$	<ul style="list-style-type: none"> <li>Activated by <math>V_{SUP\_OVH}</math> event</li> <li>From <math>V_{CPx}</math> to <math>V_{PHASEx}</math></li> </ul>	8	-	40			mA
<b>Logic IO's - FET inputs</b>									
No.64	Digital input high voltage	$V_{IN\_DIG\_H}$	<ul style="list-style-type: none"> <li>Min. voltage logical high</li> </ul>	80	-	-			% $V_{DD}$
No.65	Digital input low voltage	$V_{IN\_DIG\_L}$	<ul style="list-style-type: none"> <li>Max. voltage logical low</li> </ul>	-	-	20			% $V_{DD}$
No.66	Input pull-up resistance	$R_{IN\_DIG\_PU}$	<ul style="list-style-type: none"> <li>FETB2, FETB3-pins</li> <li>FETB1 in normal mode</li> </ul>	90	-	410			k $\Omega$ m
No.67	Input pull-down resistance	$R_{IN\_DIG\_PD}$	<ul style="list-style-type: none"> <li>FETTx-pins</li> </ul>	90	-	410			k $\Omega$ m
No.104	MISO RDSon pull-down	$R_{ON\_PD\_MISO}$	<ul style="list-style-type: none"> <li>FETB1 (MISO) in SPI mode</li> </ul>	0.5	1.1	3.4			k $\Omega$ m
No.105	MISO RDSon pull-up	$R_{ON\_PU\_MISO}$	<ul style="list-style-type: none"> <li>FETB1 (MISO) in SPI mode</li> </ul>	1.3	2.0	3.2			k $\Omega$ m
No.106	MISO source current	$I_{MISO\_SOURCE}$	<ul style="list-style-type: none"> <li>FETB1 (MISO) in SPI mode</li> </ul>	-	3	6			mA
No.107	MISO sink current	$I_{MISO\_SINK}$	<ul style="list-style-type: none"> <li>FETB1 (MISO) in SPI mode</li> </ul>	-	3	6			mA

## Datasheet

<u>Logic IO's - EN input</u>							
No.68	Input pull-down resistance	$R_{EN\_PD}$	EN	90	-	410	k $\Omega$ m
No.69	Bridge disable propagation delay	$EN_{PR\_DEL}$	From bridge disable EN < 0.2V <sub>DD</sub> to V <sub>GS</sub> < 0.5V, C <sub>LOAD</sub> = 1nF	-	-	1	$\mu$ s
<u>Logic IO's - ICOM</u>							
No.70	Pull-up current	$ICOM_{PU}$	V <sub>ICOM</sub> = 0V	-2.2	-	-5.0	mA
No.71	Pull-down current	$ICOM_{PD}$	V <sub>ICOM</sub> = V <sub>DD</sub>	5.0	-	2.6	mA
No.72	ICOM PWM frequency fast	$f_{ICOMF}$		85	100	115	kHz
No.73	ICOM PWM frequency slow	$f_{ICOMS}$		10.6	12.5	14.4	kHz
No.74	SPI start-up pulse duration on ICOM to enter SPI mode	$t_{SPI\_SU}$	EN = Low FETTx = Low, FETBx = High	2048/ f <sub>OSC</sub>	-	4096/ f <sub>OSC</sub>	s
<u>SPI Timing</u>							
No.75	SPI initial setup time	$t_{SPI\_ISU}$		2	-	-	$\mu$ s
No.76	SPI clock frequency	$f_{SPI}$		-	-	500	kHz
No.77	Rise/fall times	$t_{SPI\_RF}$	CLK, CSB, MISO, MOSI	-	-	200	ns
No.78	CSB setup time	$t_{CSB\_SU}$		1	-	-	$\mu$ s
No.79	CSB high time	$t_{CSB\_H}$		2	-	-	$\mu$ s
No.80	Clock high time	$t_{CLK\_H}$		1	-	-	$\mu$ s
No.81	Clock low time	$t_{CLK\_L}$		1	-	-	$\mu$ s
No.82	Data in setup time	$t_{DI\_SU}$		1	-	-	$\mu$ s
No.83	Data in hold time	$t_{DI\_H}$		500	-	-	ns
No.84	Data out ready delay	$t_{DO\_R}$	C <sub>LOAD</sub> at FETB1 < 50pF	-	500	-	ns
No.85	EEPROM read delay	$t_{EE\_RD}$	EE_RD = 1	6	-	-	$\mu$ s
No.86	EEPROM write delay	$t_{EE\_WR}$	EE_WR = 1	12	-	-	ms
No.87	Temperature for EEPROM read	T <sub>J,EE_RD</sub>	Junction temperature	-40	-	150	°C
No.88	Temperature for EEPROM write	T <sub>J,EE_WR</sub>	Junction temperature	-40	-	150	°C

## Datasheet

<u>Current Sense Amplifier</u>							
No.89	Input offset voltage	V <sub>IS_IO</sub>	Input differential voltage within ±100mV Common mode [-0.5, 1.0] V	-7.6	-	7.6	mV
No.90	Input offset voltage thermal drift	V <sub>IS_IO_TDRIFT</sub>		-10	-	10	µV/°C
No.91	Input common mode rejection ratio DC	I <sub>SCMRR_DC</sub>		60	-	-	dB
No.92	Input common mode rejection ratio 1MHz	I <sub>SCMRR_AC</sub>		40	-	-	dB
No.93	Input power supply rejection ratio DC for V <sub>DD</sub> supply	I <sub>SPSRR_DC</sub>		60	-	-	dB
No.94	Input power supply rejection ratio 1MHz for V <sub>DD</sub> supply	I <sub>SPSRR_AC</sub>		40	-	-	dB
No.95	Closed loop gain	I <sub>S_GAIN</sub>	Current sense gain =	-3%	80 103 133 172 222 287 370 478	+3%	
No.96	Output settling time	I <sub>S_SET</sub>	Amplified output to 99% of final value after input change	-	-	1.0	µs
No.97	Output voltage range high	V <sub>ISENSE_MAX</sub>	I <sub>SENSE</sub> output max level	V <sub>DD</sub> -0.02	-	V <sub>DD</sub>	V
No.98	Output voltage range low	V <sub>ISENSE_MIN</sub>	I <sub>SENSE</sub> output min level	GND	-	GND+0.02	V
No.99	Output short circuit current to ground	I <sub>ISENSE_SC</sub>	Output current saturation level	-	1.4	-	mA
No.100	Gain bandwidth (GBW)	I <sub>S_GB</sub>		6	-	-	MHz
No.101	Output slew rate	I <sub>S_SR</sub>		-	8	-	V/µs
No.102	CM spike recovery	I <sub>S_CM_REC</sub>	CM spike = ±1.5V, t=250ns	-	-	730	ns
No.103	V <sub>REF</sub> voltage input	V <sub>REF</sub>		0	-	50	%V <sub>DD</sub>

Table 10-1 General Electrical Specifications

## 10.1. MLX83203 Typical Performance Graphs

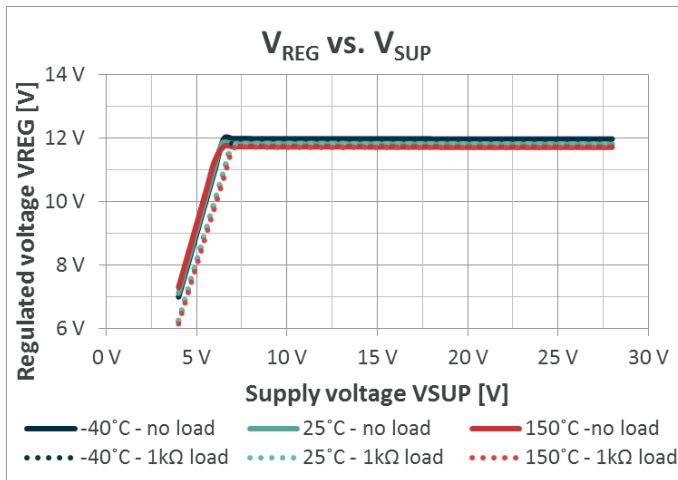


Figure 10-1 MLX83203 Regulated output voltage vs. supply voltage

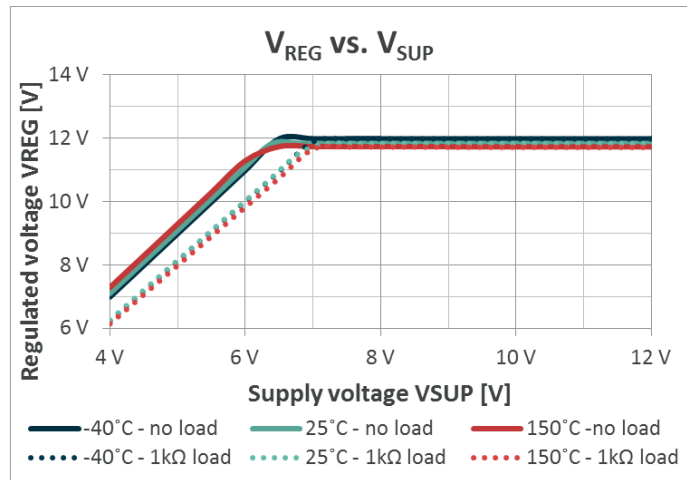


Figure 10-2 MLX83203 Regulated output voltage vs. supply voltage

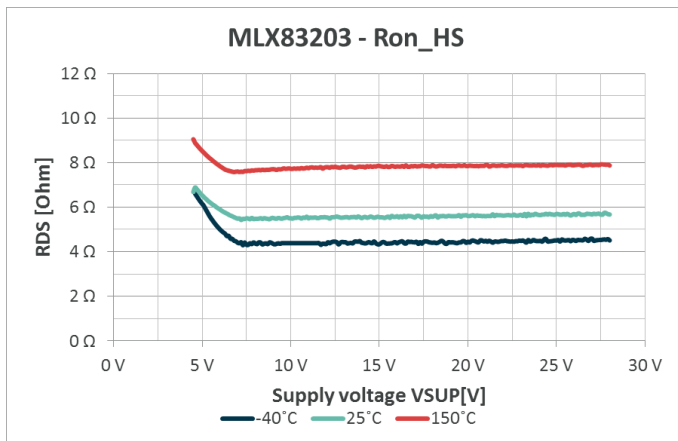


Figure 10-3 MLX83203 High-side driver FET  $R_{ON}$  resistance vs. supply voltage

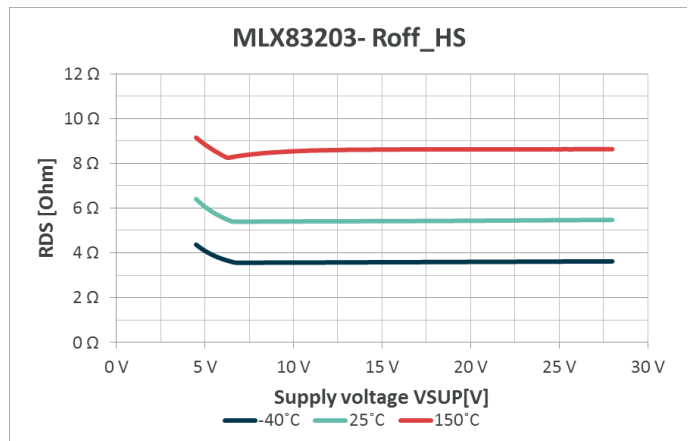


Figure 10-4 MLX83203 High-side driver FET  $R_{OFF}$  resistance vs. supply voltage

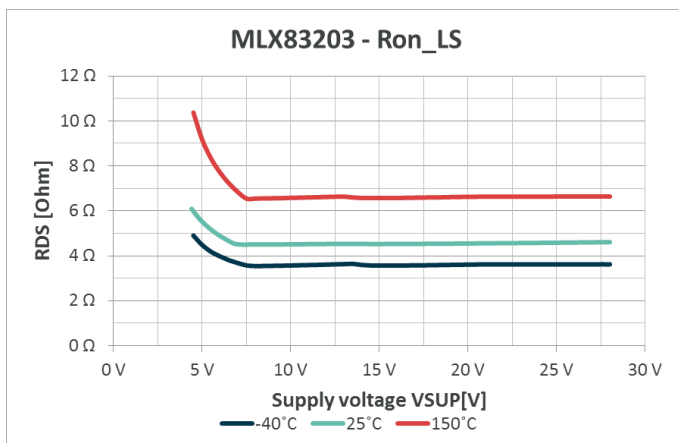


Figure 10-5 MLX83203 Low-side driver FET  $R_{ON}$  resistance vs. supply voltage

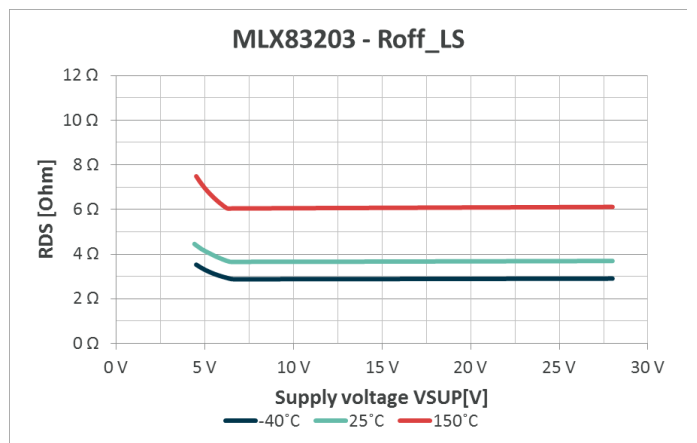


Figure 10-6 MLX83203 Low-side driver FET  $R_{OFF}$  resistance vs. supply voltage

Datasheet

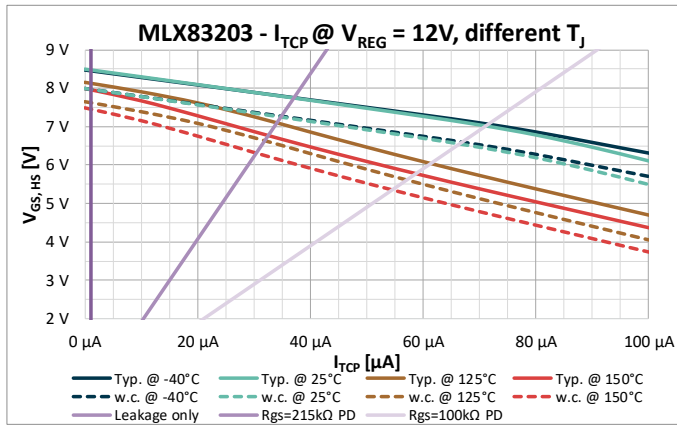


Figure 10-7 MLX83203 Trickle charge pump current capability vs gate drive voltage at different temperatures

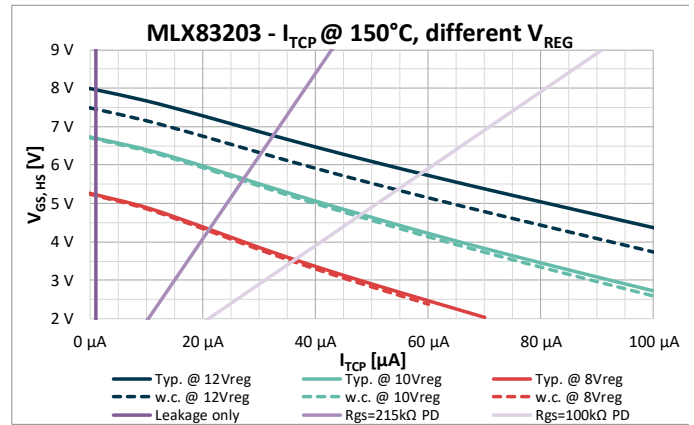


Figure 10-8 MLX83203 Trickle charge pump current capability vs gate drive voltage at different  $V_{REG}$ , at 150°C

## 10.2. MLX83202 Typical Performance Graphs

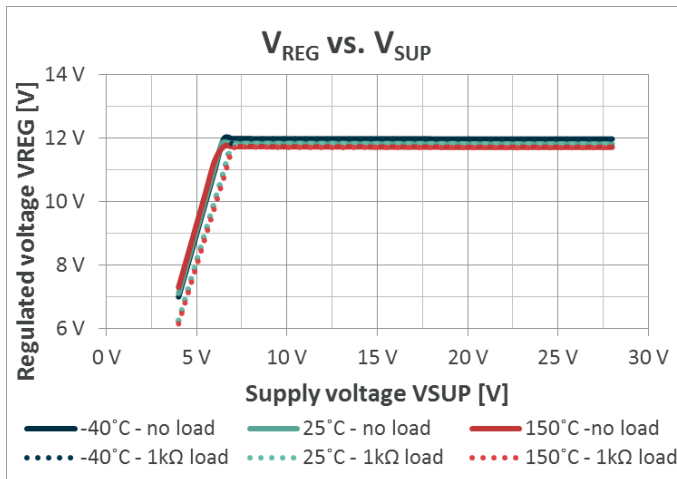


Figure 10-9 MLX83202 Regulated output voltage vs. supply voltage

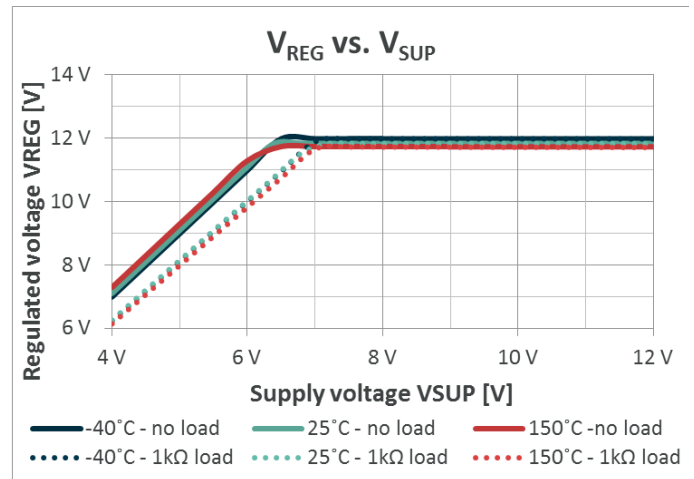


Figure 10-10 MLX83202 Regulated output voltage vs. supply voltage



Datasheet

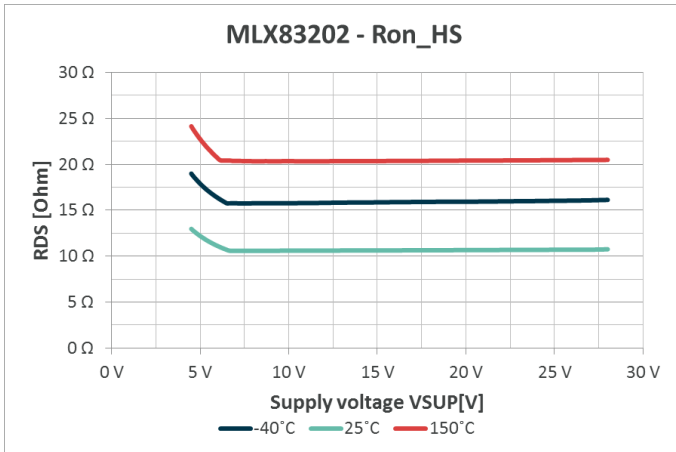


Figure 10-11 MLX83202 High-side driver FET  $R_{ON}$  resistance vs. supply voltage

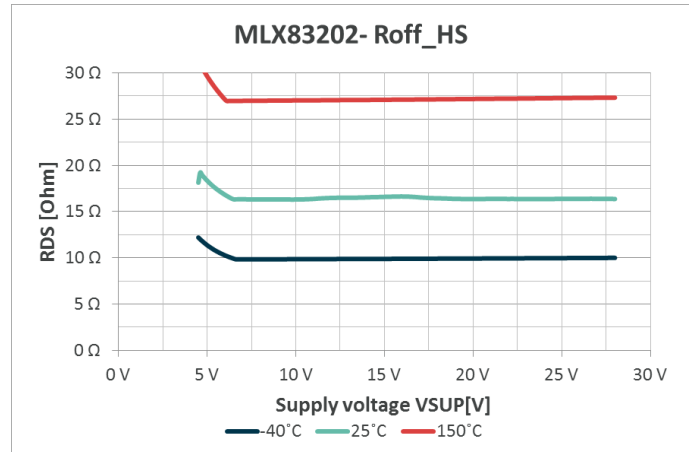


Figure 10-12 MLX83202 High-side driver FET  $R_{OFF}$  resistance vs. supply voltage

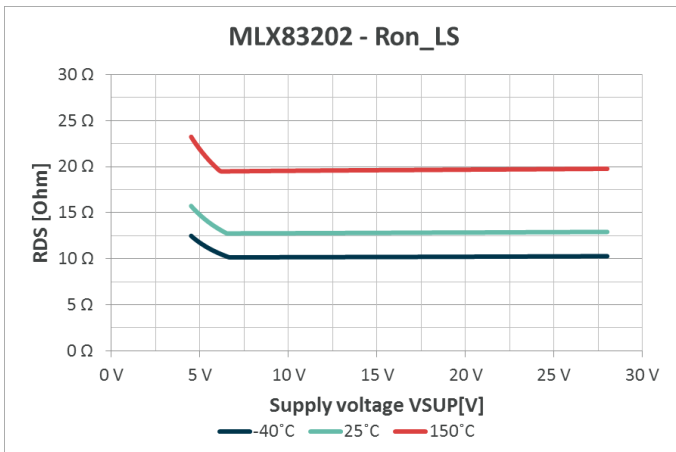


Figure 10-13 MLX83202 Low-side driver FET  $R_{ON}$  resistance vs. supply voltage

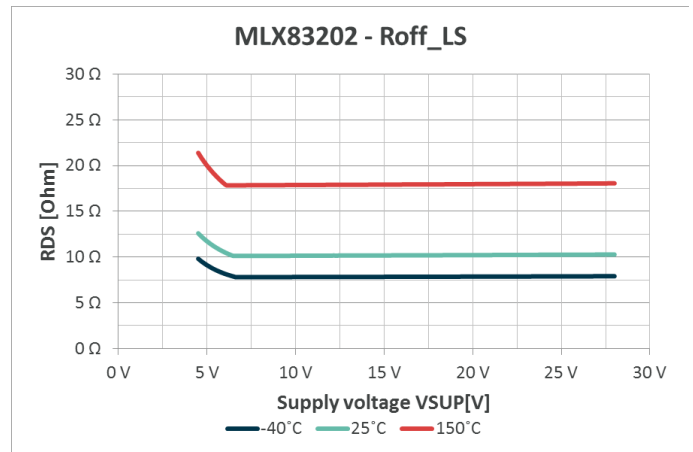


Figure 10-14 MLX83202 Low-side driver FET  $R_{OFF}$  resistance vs. supply voltage

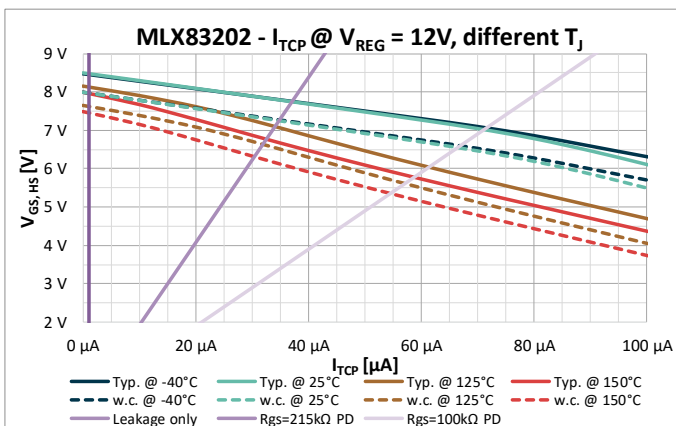


Figure 10-15 MLX83202 Trickle charge pump current capability vs gate drive voltage at different temperatures

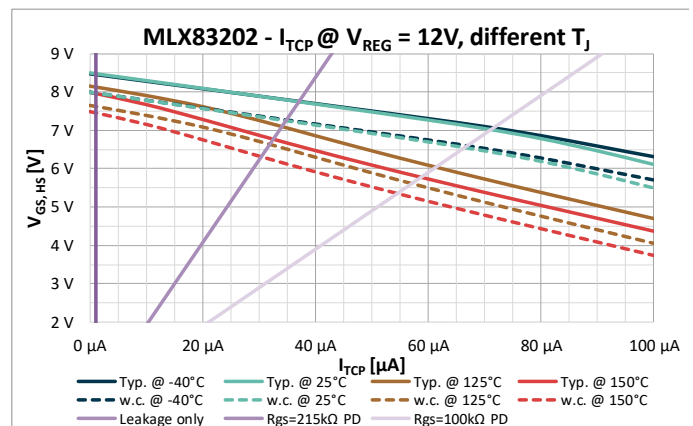


Figure 10-16 MLX83202 Trickle charge pump current capability vs gate drive voltage at different  $V_{REG}$ , at 150°C

## 11. Block Diagram

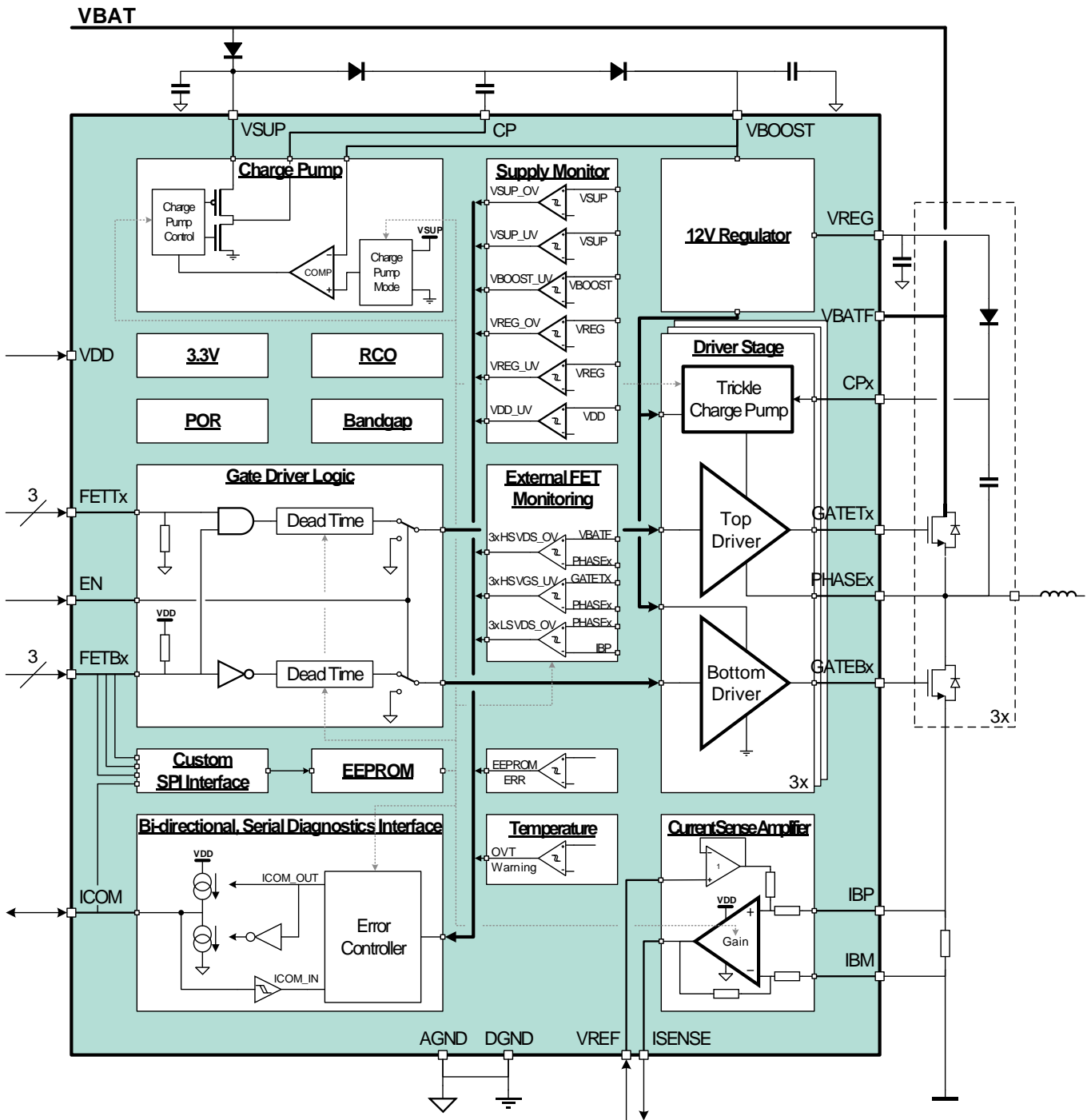


Figure 11-1 Block diagram

## 12. Functional Description

### 12.1. Supply System

The MLX83203-2 is supplied via pins VSUP and VDD. The power supply VSUP supplies the internal operation of the pre-driver, the charge pump and the voltage regulator used for the bootstrap based architecture. The digital supply VDD supplies the IO's and the current sense amplifier.

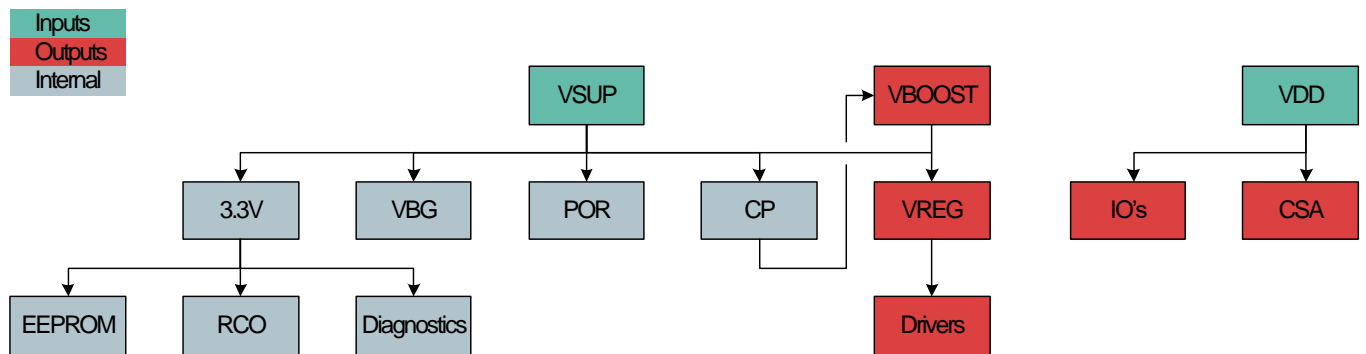


Figure 12-1 Principle organization of the supply system

#### 12.1.1. Power Supply - VSUP

The internal operation of the pre-driver is supplied from the power supply input pin VSUP. It supplies the bandgap reference, power-on-reset system and internal 3.3V regulator. This 3.3V regulator in turn supplies the EEPROM, RC-oscillator and diagnostics. For safety reasons the pre-driver provides integrated [under voltage](#) and [over voltage](#) detection on VSUP.

#### 12.1.2. Charge Pump - VBOOST

The IC comprises a charge pump, supplied from VSUP, which allows full device operation down to 4.5V. The charge pump boosted output voltage is available on VBOOST. This boosted voltage powers the voltage regulator VREG used to supply the low-side drivers directly, and high-side drivers via the bootstrap architecture. See Figure 4-1 for the standard charge pump configuration where VBOOST is regulated relative to ground. The charge pump will not be switching when  $V_{SUP} > V_{REG} + 2XV_{f, diode}$ .

An alternative mode of operation for the charge pump supports the use of an external low drop N-FET for reverse polarity protection. In this mode the charge pump boosts the output voltage relative to the supply voltage instead of relative to ground, see application diagram in Figure 4-2. The disadvantage is an additional amount of dissipation inside the driver to regulate VREG.

The charge pump architecture is a supply voltage doubler with feedback loop for stable output voltage generation, as shown in Figure 12-2. It can be configured in EEPROM to either regulate the boosted output voltage VBOOST relative to ground or relative to the supply voltage, see Figure 12-3 for the typical output voltage. Furthermore the EEPROM configuration allows disabling the charge pump for applications not requiring the low voltage operation, in order to reduce the overall power consumption.

## Datasheet

For safety reasons the pre-driver provides integrated [under voltage](#) detection on VBOOST. In addition the charge pump comprises a discharge switch in order to keep VBOOST output voltage in a safe operating area in case of over voltage on the supply input pin. The discharge switch is activated as soon as the supply voltage VSUP exceeds the  $V_{SUP\_OVH}$  threshold level and is deactivated when it drops below the  $V_{SUP\_OVL}$  threshold. At the same time the charge pump is deactivated.

EN_CP	CPMODE	Charge pump configuration
0	x	Charge pump disabled
1	0	Charge pump configured to regulate VBOOST relative to ground, to support low voltage operation
1	1	Charge pump configured to regulate VBOOST relative to the supply, to support the use of a reverse polarity N-FET

Table 12-1 Charge pump configuration options

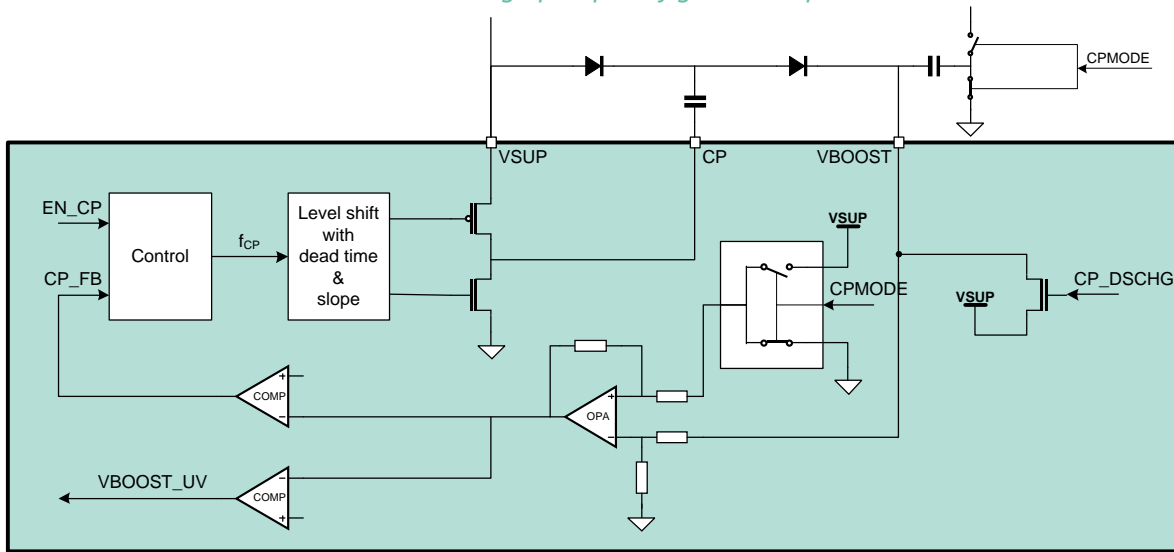


Figure 12-2 Charge pump principle schematic

### Charge Pump and Voltage Regulator Output vs Power Supply Input

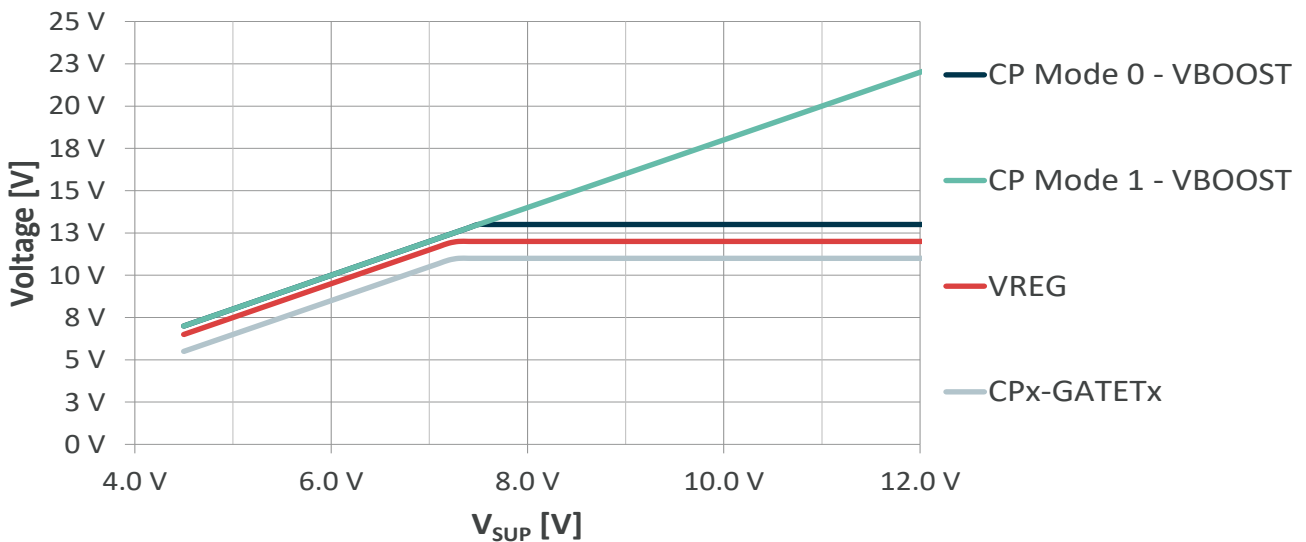


Figure 12-3 Charge pump output and driver supply

### 12.1.3. Voltage Regulator - VREG

The voltage regulator regulates the power supply down to 12V, in order to supply the low-side gate drivers and switch the external low-side N-FETs without gate-source over voltage at high battery voltages. The regulated output voltage VREG further provides the bootstrap voltage for driving the high-side N-FETs.

For safety reasons the pre-driver provides integrated [under voltage](#) and [over voltage](#) detection on VREG.

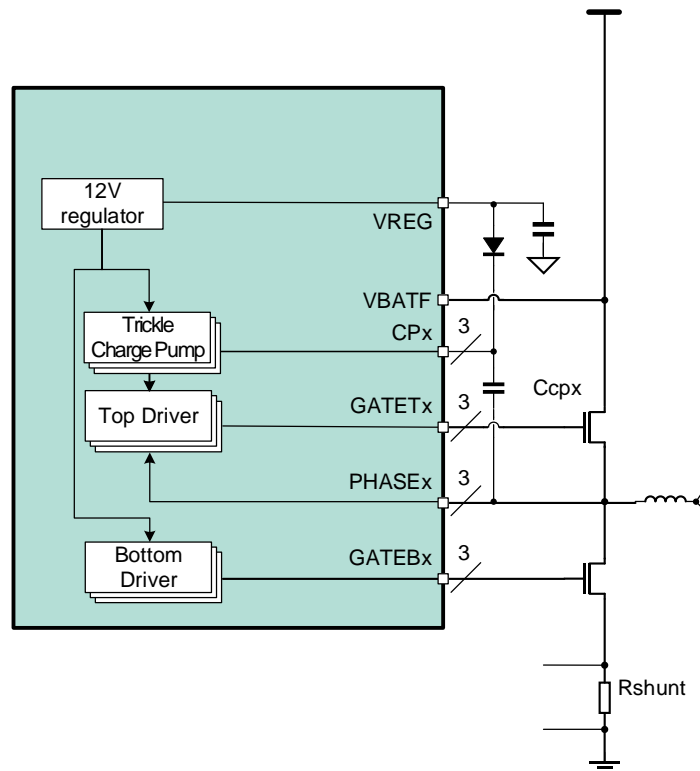


Figure 12-4 Voltage regulator for driver supply – VREG

### 12.1.4. Digital Supply - VDD

The MLX83203-2 comprises a current sense amplifier. The current sense amplifier and IO's are supplied from the digital supply VDD.

For safety reasons the pre-driver provides integrated [under voltage](#) detection on VDD.

#### **Note:**

When supplying VDD with a limited output impedance (e.g. from a microcontroller IO) the performance of the amplifier may be affected.

### 12.1.5. Sleep Mode

Sleep mode is activated when the digital supply input VDD is pulled below “VVDD sleep voltage threshold low”. In sleep mode the charge pump is disabled and the current consumption on VSUP is reduced. All gate drivers are switched off via sleep gate discharge resistors  $R_{SGD}$ . The pre-driver will wake-up as soon as the voltage level on VDD rises above “VVDD sleep voltage threshold high”.

## Datasheet

Pin Name	State in sleep mode
CP	The charge pump is disabled.
VBOOST	Since the charge pump is disabled VBOOST is pulled to the supply voltage via the external charge pump diodes.
GATEBx	In sleep mode, gate-discharge resistors ( $R_{SGD}$ ) between GATEBx and DGND are activated, ensuring all low-side gate drivers are switched off
GATETx	In sleep mode, gate-discharge resistors ( $R_{SGD}$ ) between GATETx and PHASEx are activated, ensuring all high-side gate drivers are switched off
PHASEx	Phases are kept low with GATETx through the internal body diode of the pre-driver
VREG	Voltage regulator is disabled
CPx	Any charge that remains after VREG is disabled will leak to ground
ISENSE	Current sense amplifier is supplied from VDD, and thus not active
FETBx, FETTx EN, ICOM	All IO's are supplied from VDD, and thus not active

Table 12-2 Drivers in Sleep Mode

### Notes:

1. In case any of the digital input pins are externally pulled high while VDD is low, current will flow into VDD via [internal ESD protection diodes](#). This condition is not allowed.
2. When VDD is pulled low, also ICOM will go low. This should not be interpreted as a diagnostic interrupt.

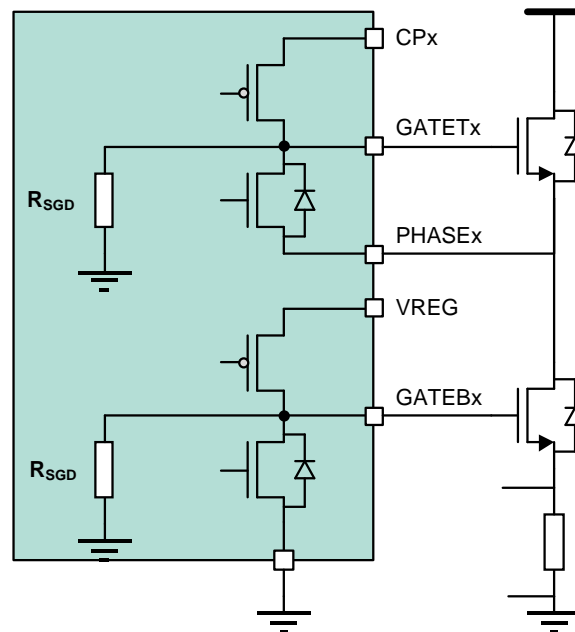


Figure 13-1-5 Drivers in Sleep Mode

## 12.2. Gate Drivers

### 12.2.1. PWM Input Control Logic – FETBx & FETTx

Each of the 6 external N-FETs can be controlled independently via the 6 digital PWM input pins: FETBx and FETTx. However, the digital logic provides the option to control the 3 external half bridges with only 3 control signals, by shorting high-side and low-side PWM input pins for each half bridge.

The IC provides internal shoot through protection since the digital logic prevents simultaneous activation of both high-side and low-side driver of one half bridge. A configurable [dead time](#) ensures the high-side (low-side) N-FET is fully switched off, before switching on the complementary low-side (high-side) N-FET.

For safety reasons the pre-driver provides [integrated drain-source](#) and [gate-source monitoring](#) for each of the 6 external N-FETs.

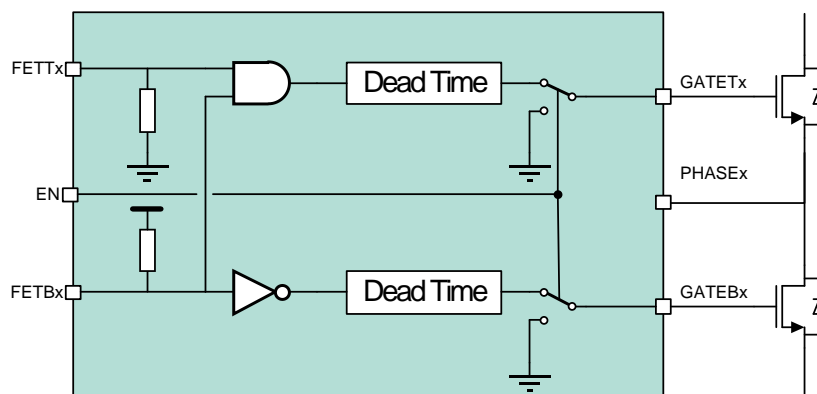


Figure 12-5 Input control logic of the driver stage

### 12.2.2. Enable Input EN

The enable input pin EN enables the gate driver outputs when set high. When reset, all gate driver outputs are switched to the low state, switching off all external N-FETs. This is performed by pulling all gate drivers to ground via the pull-down on-resistances. The enable pin can be used by the microcontroller to disable all drivers in case of any fault detection.

While EN is low, the programming of the EEPROM via SPI can be initiated by pulling ICOM low for the SPI start-up time specified by [t<sub>SPI\\_SU</sub>](#).

### 12.2.3. Gate Driver Supply and Bootstrap Architecture – VREG & CPx

[The voltage regulator](#) regulates the power supply voltage down to 12V. The regulated voltage is used to directly supply the low-side drivers. To provide sufficient supply voltage for the high-side drivers a bootstrap architecture is used. When the low-side N-FET is switched on, the phase voltage will be pulled low and the bootstrap capacitor is charged from the VREG buffer capacitor through the bootstrap diode. Afterwards, if the low-side N-FET is switched off and the high-side N-FET is switched on, the charge of the bootstrap capacitor is used to supply sufficient gate drive voltage to the high-side N-FET. The integrated trickle charge pump assures the bootstrap capacitor will not be discharged, and allows 100% PWM operation.

## 12.3. Integrated Current Sense Amplifier

The IC comprises an integrated fast, high-bandwidth, low offset current sense amplifier.

The current sense amplifier is supplied from the digital supply. It senses the voltage over the low-side shunt, amplifies it with the [gain programmed in EEPROM](#) and adds the offset provided on VREF. The output of the amplifier is available on ISENSE.

$$ISENSE = Current \times Shunt \times Gain_{EEPROM} + V_{VREF}$$

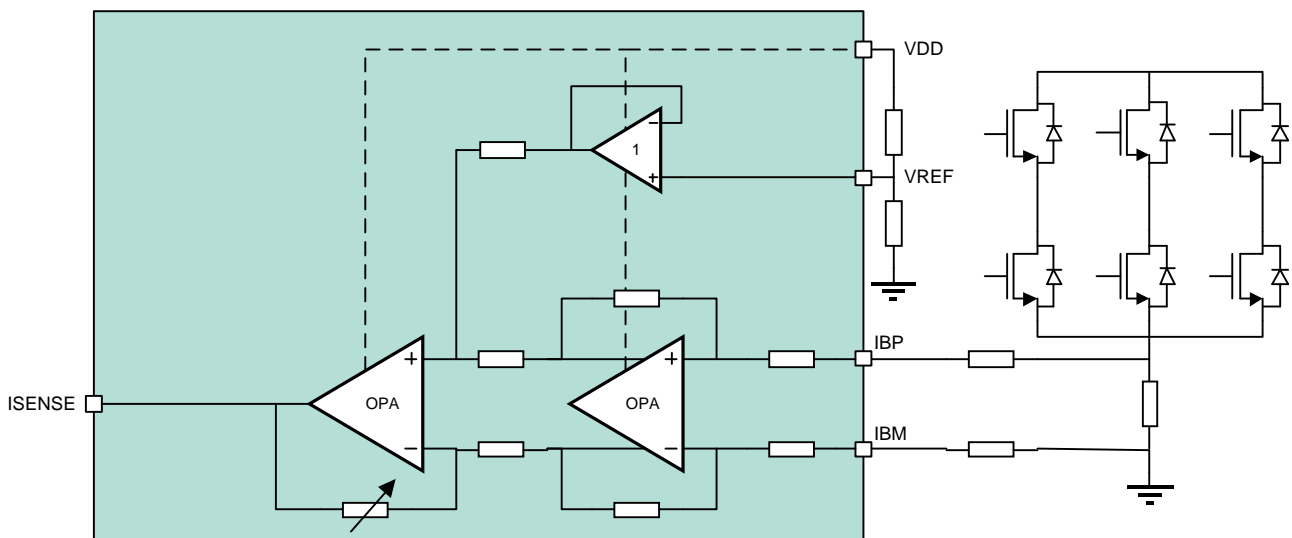


Figure 12-6 Current Sense Amplifier



## 12.4. Protection and Diagnostic Functions

### 12.4.1. Power Supply Over Voltage Shutdown (VSUP\_OV)

The pre-driver has an integrated [VSUP over voltage shut down](#) to prevent destruction of the IC at high supply voltages.

### 12.4.2. Power Supply Under Voltage Warning (VSUP\_UV)

The pre-driver has an integrated [VSUP under voltage detection](#). The diagnostics interface will give a warning to the microcontroller. It is the responsibility of the microcontroller to take action in order to ensure reliable operation.

### 12.4.3. Digital Supply Under Voltage Warning (VDD\_UV)

The pre-driver has an integrated [VDD under voltage detection](#). The diagnostics interface will give a warning to the microcontroller. It is the responsibility of the microcontroller to take action in order to ensure reliable communication between microcontroller and pre-driver.

### 12.4.4. VBOOST Under Voltage Warning (VBOOST\_UV)

The integrated charge pump boosts the supply voltage in low voltage operation on the VBOOST output. There is an [under voltage detection on VBOOST](#) to warn the microcontroller the charge pump is not ready. It is the responsibility of the microcontroller to take action in order to ensure reliable motor operation.

### 12.4.5. Gate Driver Supply Over Voltage Warning/Shutdown (VREG\_OV)

The MLX83203-2 comprises an integrated [VREG over voltage detection](#). The reaction of the pre-driver on this VREG\_OV event depends on the status of the [Bridge Feedback](#) bit in EEPROM. If this VREG\_OV\_BF\_EN bit is set the pre-driver will disable all gate drivers, switching off all external N-FETs. If the bit is reset it will just give a warning to the microcontroller.

VREG_OV_BF_EN	Pre-driver reaction VREG_OV event
0	VREG_OV is reported on ICOM, but the drivers remain active
1	VREG_OV is reported on ICOM and the drivers are disabled

*Table 12-3 EEPROM Configuration for VREG over voltage detection*

### 12.4.6. Gate Driver Supply Under Voltage Warning (VREG\_UV)

The pre-driver detects when the regulated voltage drops below [the under voltage threshold](#). The diagnostics interface will give a warning to the microcontroller. It is the responsibility of the microcontroller to take action in order to ensure reliable switching of the external N-FETs, since the VREG voltage directly supplies the low-side gate drivers.

### 12.4.7. Gate Source Voltage Monitoring Warning (VGS\_UV)

In order to ensure reliable switching of the high-side N-FETs, the MLX83203-2 comprises gate-source monitors for each of the high-side N-FETs. In case of an [under voltage](#), the diagnostics interface will give a warning to the microcontroller, if the [gate-source comparators are enabled in EEPROM](#). It is the responsibility of the microcontroller to take action in order to ensure reliable switching of the high-side gate drivers.

### 12.4.8. Over Temperature Warning (OVT)

If the junction temperature exceeds the specified [threshold](#), a warning will be communicated to the microcontroller. The pre-driver will continue in normal operation. It is the responsibility of the microcontroller to protect the IC against over temperature destruction.

### 12.4.9. Shoot Through Protection and Dead Time

The pre-drivers' [internal implementation](#) guarantees that low-side and high-side N-FET of the same external half bridge cannot be conducting at the same time, preventing a short between the supply and ground. In addition the pre-driver provides a [programmable dead time](#) in EEPROM. The dead time sets the delay between the moment when the high-side (low-side) N-FET is switched off, and the moment when the complementary low-side (high-side) N-FET can be switched on.

### 12.4.10. Drain-Source Voltage Monitoring Warning/Shutdown (VDS\_ERR)

The MLX83203-2 provides a [drain-source voltage monitoring](#) feature for each external N-FET to protect against short circuits to ground or supply. For the high-sides the drain-source voltage are sensed via the VBATF –and PHASEx-pins. For the low-sides the PHASEx –and IBP-pins are used. The [drain-source voltage comparator](#) can be enabled or disabled in EEPROM.

The drain-source voltage monitor for a certain external N-FET is activated when the corresponding input is switched on and the dead time has passed. An additional [blanking time](#) can be programmed in EEPROM. If the drain-source voltage remains higher than the [VDS monitor threshold voltage](#), the VDS error is raised. The threshold voltage is configurable in EEPROM.

The reaction of the pre-driver on a VDS error can be configured in EEPROM with the [Bridge Feedback](#) bit. If this bit is set the pre-driver automatically disables the drivers when a VDS error is detected. If the bit is reset, the drivers remain active. In both cases the VDS error will be reported to the microcontroller.

VDS_COMP_EN	VDS_BF_EN	Pre-driver reaction on VDS-error event
0	x	Any VDS error is ignored and no error is reported on ICOM
1	0	VDS_ERR is reported on ICOM, but the drivers remain active
1	1	VDS_ERR is reported on ICOM and the drivers are disabled

*Table 12-4 EEPROM Configuration for drain-source error detection*

### 12.4.11. EEPROM Error Warning (EEP\_ERR)

To ensure reliable communication with EEPROM the pre-driver provides an automatic single bit error correction and double error detection. If two bits in the addressed word are bad the EEPROM gives the EEP\_ERR warning, indicating a double error was detected.

### 12.4.12. Diagnostics Interface – ICOM

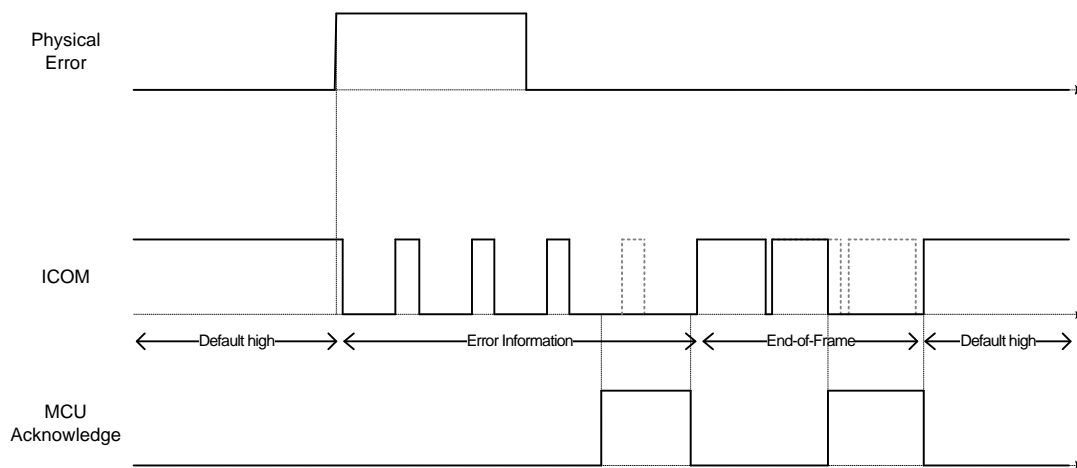
All diagnostic events described above are reported to the microcontroller via a single pin, ICOM. In normal operation, when no error is detected, ICOM is default high.

The ICOM interface acts as a serial interface that feeds back detailed diagnostics information. If an error is detected, ICOM goes from default high to [communicating a PWM-signal](#). The speed of this PWM signal depends on the EEPROM configuration of bit [PWM\\_SPEED](#). Each error corresponds to a duty cycle with a 5-bit resolution. Thus the microcontroller can distinguish different errors by reading the duty cycle, see Table 12-7.

PWM_SPEED	Description
0	Slow mode: for slow microcontrollers
1	Fast mode : for fastest response of microcontroller

*Table 12-5 EEPROM Configuration for diagnostics communication speed*

The duty cycle is transmitted until the microcontroller sends the acknowledgement. This is done by pulling ICOM low for more than a PWM-period,  $t_{Ack} > t_{ICOM}$ . At each ICOM falling edge the pre-driver checks the actual voltage on ICOM in order to detect an acknowledgement. After acknowledgement the duty cycle of the next error is transmitted, if multiple errors were detected. All errors have been reported when the end-of-frame duty cycle is send. When all errors are physically removed, and the end-of-frame message is acknowledged by the microcontroller, ICOM returns to its default high state.



*Figure 12-7 ICOM Diagnostics Communication*

## Datasheet

### Notes:

1. When VDD is pulled low to put the pre-driver in sleep mode, ICOM will go low as well. This should not be interpreted as a diagnostic interrupt. As soon as VDD goes high, the pre-driver wakes-up and ICOM will return to its default high state.
2. At POR it is possible that the voltages on VSUP and VREG were not above the under voltage thresholds (e.g. due to charging of external capacitors). It is possible that ICOM reports these under voltage errors after POR. This implies that the microcontroller has to acknowledge these errors before ICOM will be in its default high state and the pre-driver is ready for normal operation.

The drivers are disabled when	The drivers are enabled again as soon as
An error condition is detected for which the hardware protection is activated VSUP_OV VREG_OV VDS_ERR	The microcontroller acknowledges the error
VDD = Low (sleep mode)	VDD = High (wake-up)
EN = Low	EN = High

Table 12-6 Pre-Driver Output State Summary

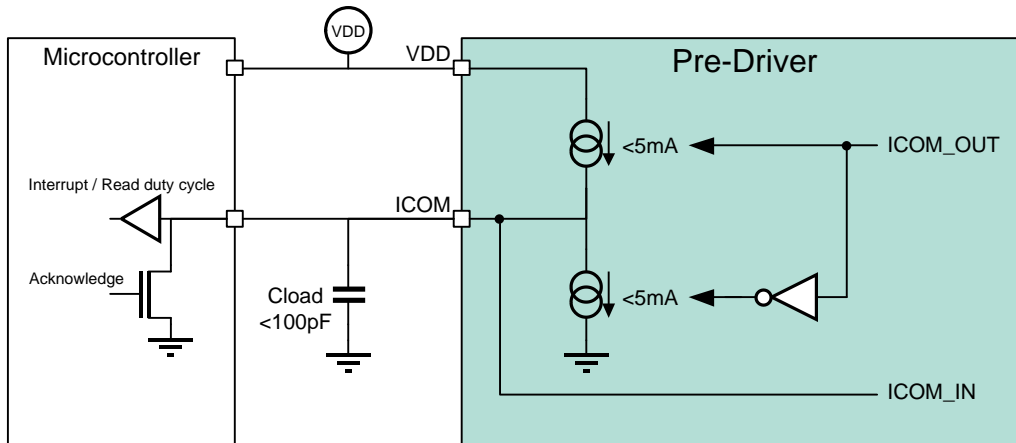


Figure 12-8 ICOM Diagnostics Interface

In case multiple errors occur at the same time, the priority is as defined in Table 12-7. The highest priority is 0 and 16 is the lowest priority.

## Datasheet

Priority	Error Event	% Duty Cycle	Debounce Time	Description
11	ICOM_EOF	94.44 % ( $\pm 1\%$ )	n/a	End of frame
				VDS Error = VDS_T1   VDS_T2   VDS_T3   VDS_B1   VDS_B2   VDS_B3
10	VDS_ERR	83.33 % ( $\pm 1\%$ )	2 $\mu$ s	<p>This event can be masked by setting VDS_COMP_EN = 0</p> <p>To avoid erroneous triggering due to switching there is a programmable blanking time on top of the debounce time: VDS_BLANK_TIME[1:0].</p>
9	EEP_ERR	55.56 % ( $\pm 1\%$ )	n/a	EEPROM dual error detected
8	VDD_UV	50.00 % ( $\pm 1\%$ )	8 $\mu$ s	VDD under voltage
7	VSUP_OV	44.44 % ( $\pm 1\%$ )	2 $\mu$ s	VSUP over voltage
6	VSUP_UV	38.89 % ( $\pm 1\%$ )	8 $\mu$ s	VSUP under voltage
5	OVT	33.33 % ( $\pm 1\%$ )	2 $\mu$ s	OVT over temperature
4	VREG_UV	27.78 % ( $\pm 1\%$ )	16 $\mu$ s	VREG under voltage
				VGS under voltage
3	VGS_UV	22.22 % ( $\pm 1\%$ )	2 $\mu$ s	<p>This event can be masked by setting VGS_UV_COMP_EN = 0</p>
2	VBOOST_UV	16.67 % ( $\pm 1\%$ )	16 $\mu$ s	VBOOST under voltage
				VREG over voltage
1	VREG_OV	11.11 % ( $\pm 1\%$ )	2 $\mu$ s	<p>This event can be masked by setting VGS_UV_COMP_EN = 0</p>

Table 12-7 Overview Diagnostics over ICOM with Priority Definitions

## 12.5. EEPROM Configuration

The MLX83203-2 provides an EEPROM for configuration of the IC, the current sense amplifier and over current comparator, protection and diagnostic functions. This allows to optimize the pre-drivers' operation for the application requirements. The configuration can be done at customer production testing by using the PTC-04, or by the microcontroller via a custom program interface.

The EEPROM features [single error correction and double error detection](#).

### 12.5.1. Memory Map

The MLX83203-2 comprises 6 bytes of EEPROM for user configurability. The first two bytes are not used for the internal configuration of the pre-driver, and can thus be used by the customer for traceability purposes. The other 4 bytes are used for configuration of the current sense amplifier and configuration of the diagnostics.

The pre-driver is programmed with default settings per table below.

Address	ED7	ED6	ED5	ED4	ED3	ED2	ED1	ED0
0	-	-	-	-	-	-	-	MLX
0x00	0	0	0	0	0	0	0	0
1	-	-	-	-	-	-	-	MLX
0x00	0	0	0	0	0	0	0	0
2	DEAD_TIME[2:0]		VDSMON[2:0]			CPMODE	MLX	
0x7C	011		111			0	0	
3	VDS_BLANK_TIME[1:0]	PWM_SPEED	-	CUR_GAIN[2:0]		MLX		
0x86	10	0	0	011		0		
4	VREG_OV _BF_EN	VDS _BF_EN	VDS _COMP_EN	VGS_UV _COMP_EN	EN_TCP	EN_CP	-	MLX
0xF4	1	1	1	1	0	1	0	0
5(-6-7)	SPI_EN	MLX	-	-	-	-	-	MLX
0xC0	1	1	0	0	0	0	0	0

*Table 12-8 EEPROM Memory Map and Default Configuration*

## Datasheet

Bit Name	Description	Default
<b>Configuration of the IC</b>		
<a href="#">CPMODE</a>	Defines the mode of operation of the internal charge pump 1: VBOOST voltage is regulated relative to VSUP for reverse polarity N-FET protection 0: VBOOST voltage is regulated relative to GND for low voltage operation with minimal power consumption	0
<a href="#">EN_CP</a>	Defines the status of the pre-drivers' internal charge pump 1: Charge pump active 0: Charge pump not active	1
<a href="#">EN_TCP</a>	Defines the status of the pre-drivers' trickle charge pump 1: Trickle charge pump active 0: Trickle charge pump not active	0
<a href="#">SPI_EN</a>	Defines the accessibility of EEPROM through the custom SPI interface 1: EEPROM accessible via the custom SPI interface 0: EEPROM not accessible via the custom SPI interface	1
<b>Configuration of the Current Sense Amplifier and Over Current Comparator</b>		
<a href="#">CUR_GAIN[2:0]</a>	Defines the gain of the current sense amplifier	011
<b>Configuration of the Protection and Diagnostic Functions</b>		
<a href="#">PWM_SPEED</a>	Defines the diagnostics communication speed on ICOM 1: Fast mode for fastest response of microcontroller 0: Slow mode for low-end microcontrollers	0
<a href="#">VREG_OV_BF_EN</a>	Defines the pre-drivers' reaction on a regulated supply over voltage: 1: Report VREG_OV on ICOM and disable gate drivers 0: Report VREG_OV on ICOM without effect on gate drivers	1
<a href="#">DEAD_TIME[2:0]</a>	Defines the dead time between switching off high-side (low-side) N-FET and switching on complementary low-side (high-side) N-FET	011
<a href="#">VDSMON[2:0]</a>	Defines the threshold level for the VDS monitoring of the external N-FETs	111
<a href="#">VDS_BLANK_TIME[1:0]</a>	Defines the duration of the VDS blanking time after switching on the N-FET	10
<a href="#">VDS_COMP_EN</a>	Defines the status of the pre-drivers' drain-source monitoring 1: Drain-source comparators active 0: Drain-source comparators not active	1
<a href="#">VDS_BF_EN</a>	Defines the pre-drivers' reaction on a drain-source fault: 1: Report VDS_ERR on ICOM and disable gate drivers 0: Report VDS_ERR on ICOM without effect on gate drivers	1
<a href="#">VGS_UV_COMP_EN</a>	Defines the status of the pre-drivers' gate-source monitoring 1: Drain-source comparators active 0: Drain-source comparators not active	1

Table 12-9 EEPROM Bit Description

### 12.5.2. “SPI Program Mode”

The EEPROM memory can be accessed through a custom SPI interface. It allows the user to read/program the EEPROM by the microcontroller in the application. This custom interface re-uses the low-side driver pins for SPI communication.

Since the same pins are used for both reading/writing the EEPROM and for controlling the motor, the EEPROM is only accessible when the motor is not running. Furthermore it is necessary to apply a certain sequence of conditions before the pre-driver will enter the “SPI Program Mode”. Once in this mode, the EEPROM can be accessed for reading and writing, until the IC enters “Normal Mode” again and motor operation is possible.

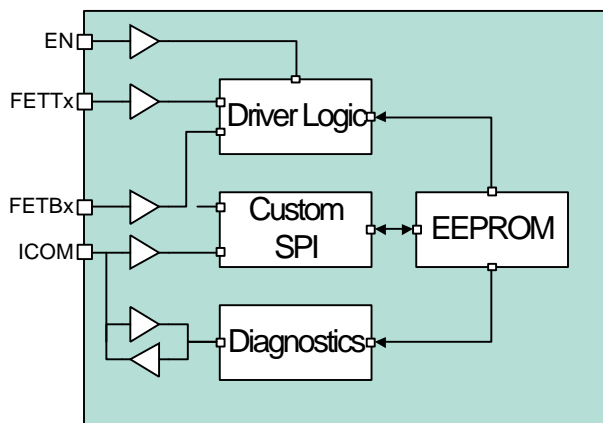


Figure 12-9 Custom SPI interface

Pin Name	SPI Signal	Description
ICOM	CSB	SPI-frames are defined by CSB low
FETB3	MOSI	The MOSI (Master Out – Slave In) shift register is reading in data on the rising edge of CLK
FETB2	CLK	Clock input, each SPI-frame has to consist of 16 clock periods
FETB1	MISO	The MISO (Master In – Slave Out) output is guaranteed to be stable while the CLK is low

Table 12-10 SPI Signals

The EEPROM controller refreshes the registers with the EEPROM conf. every 2ms (with same accuracy as the RCO). The loading of the EEPROM configuration in the configuration registers takes <100µs. During this loading, entry in SPI is forbidden, to guarantee valid data in the registers and to prevent the digital getting in a locked stage. If the pre-driver is in a locked stage, a POR is necessary. Therefore entry in SPI is advised after POR in a fixed window, as defined in Figure 12-10.

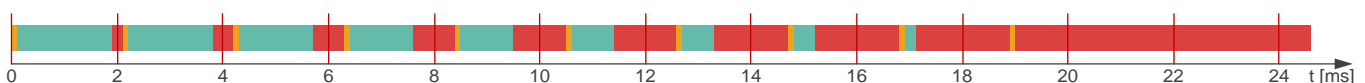


Figure 12-10 Entry in SPI mode after POR

(green = safe zone to enter SPI mode, red = accuracy of the 2ms timer, orange = loading time of 100µs)



## Datasheet

### 12.5.2.1. Entering “SPI Program Mode”

The MLX83203-2 enters “[SPI Program Mode](#)” when all below conditions are satisfied.

- ICOM
  - Any pending errors have been removed and acknowledged, so ICOM is in default high state
  - A low level pulse is applied on ICOM for a time  $t_{SPI\_SU}$   
At the end of this pulse, the rising edge, below conditions are checked as well
- EN = 0
- FETTx = Low (High-side FET inputs off) & FETBx = High (Low-side FET inputs off)

**Note:** To enter “[SPI Program Mode](#)” the MCU has to pull the FETB1-pin high. When the pre-driver enters this mode, the FETB1-pin becomes the MISO push-pull output pin with default low state. The MCU should release the FETB1/MISO-pin as soon as possible, as a current may be flowing from the MCU pin to the pre-driver pin. Make sure the current does not exceed the pre-drivers’ max. specified MISO sink current and check potential effects on microcontroller side.

### 12.5.2.2. Exiting “SPI Program Mode”

The MLX83203-2 will exit the “SPI Program Mode” when the enable input EN is pulled high. Similar to when the MLX83203-2 comes out of POR, after leaving the “SPI Program Mode” the pre-driver is blocked until the data have been copied to the registers. Meaning that before entering “Normal Mode” the EEPROM write will be completed and the EEPROM state machine will copy all EEPROM contents into registers. During this time ICOM is kept low. When it returns to its default high state the pre-driver is ready for normal operation.

### 12.5.2.3. Protocol

Once the IC is in “SPI Program Mode” the microcontroller can read/write the EEPROM, following the protocol depicted below.

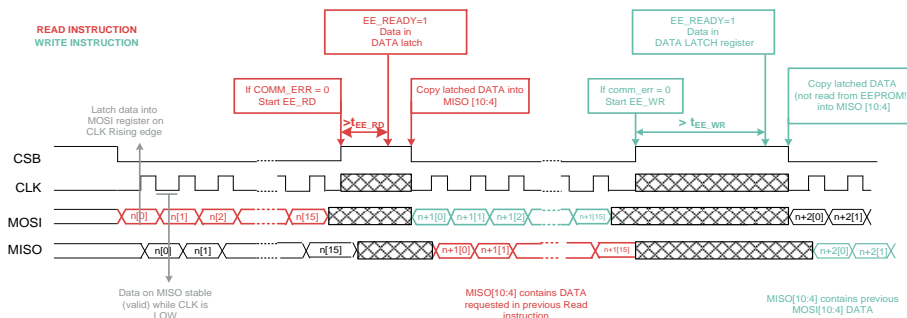


Figure 12-11 SPI Protocol (LSB first)

### 12.5.2.4. Registers Description

MOSI [15:0]							
Bit [15]	Bit [14]	Bit [13]	Bit [12]	Bit [11]	Bit [10]	Bit [9]	Bit [8]
MOSI_PAR	x	x	CMD [1:0]		MOSI_DATA [7:5]		
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
MOSI_DATA [4:1]				x	ADDRESS [2:0]		

Table 12-11 MOSI frame description

## Datasheet

MISO[15:0]							
Bit [15]	Bit [14]	Bit [13]	Bit [12]	Bit [11]	Bit [10]	Bit [9]	Bit [8]
MISO_PAR	COMM_ERR	EE_READY	CMD [1:0]		MISO_DATA [7:5]		
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
MISO_DATA [4:1]			x		ADDRESS [2:0]		

Table 12-12 MISO frame description

Bit	Description
ADDRESS	Address of the byte in EEPROM that needs to be read/written to.
MOSI_DATA[7:1]	In case of write command, the data that needs to be written. Don't care for any read command.
MISO_DATA[7:1]	In case previous command was write instruction, it returns the data that was written. In case of a read instruction, it returns the data read from EEPROM.
CMD [1:0]	Read/Write command 00: EE_RD: Read command 01: EE_WR: Write command 10: EE_RDAW1 11: EE_RDAW2
EE_READY	Reading/writing the EEPROM takes a certain time, specified by <a href="#">t<sub>EE_RD</sub></a> and <a href="#">t<sub>EE_WR</sub></a> respectively. These times define the minimum time CSB (ICOM) has to remain high between two SPI-frames in order to finish the read/ write action.  As soon as the read/write action starts, the EE_READY bit is reset. After completion of the read/write action the bit is set.  If the read/write delay between SPI-frames was long enough to execute the read/write action, the EE_READY bit will thus be set, signaling the read/write action was finished. If the time was too short, the bit will still be 0.
COMM_ERR	This bit indicates if the previous MOSI-frame was received correctly. If no communication error occurred the bit will be reset, and the read/write action was started as soon as CSB was pulled high.  If a communication error occurred in the previous MOSI-frame the read/write command was not executed. Possible communication errors are: Odd parity bit was set incorrect Number of clock periods was not equal to 16
MOSI_PAR, MISO_PAR	Odd parity bit of the current MOSI/MISO frame.

Table 12-13 MOSI/MISO frames bit description

Datasheet

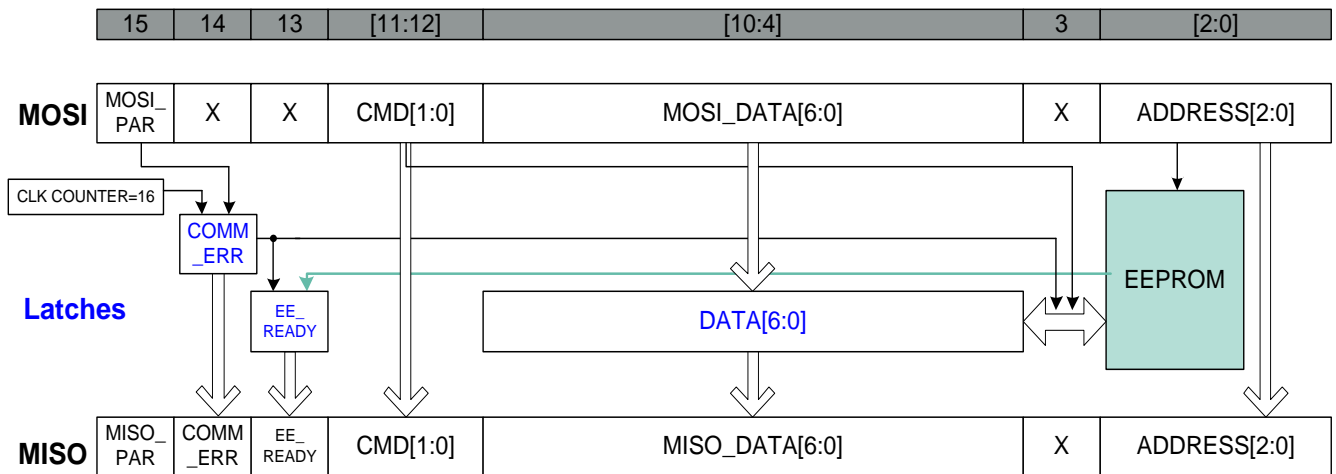


Figure 12-12 MOSI/MISO registers and relation to internal data latches

### 12.5.2.5. Read Instruction

In order to read one of the EEPROM bytes, the microcontroller should compose the MOSI(N) frame according to Table 12-11 with the address it wants to read, the read command and set the odd parity bit in a correct way.

After transmission of this MOSI(N)-frame and when the CSB signal is pulled high, the pre-driver will start to read the data at the specific address. If CSB is kept high long enough for the pre-driver to execute the read action, it will transmit the read data on the next MISO(N+1)-frame.

The data in this MISO(N+1)-frame is valid only if

- COMM\_ERR = 0 : no communication error was detected on the previous MOSI(N)-frame
- EE\_READY = 1 : the read delay was long enough to finish the read
- MISO\_PAR = correct : the MISO(N+1)-frame has a correct odd parity bit

### 12.5.2.6. Write Instruction

The MLX83203-2 provides different configuration options through the EEPROM programming. In order to program one of the EEPROM bytes, the microcontroller should compose the MOSI(N) frame according to Table 12-11 with the address and data it wants to write, the write command and set the odd parity bit in a correct way.

After transmission of this MOSI(N)-frame and when the CSB signal is pulled high, the pre-driver will start to write the data at the specific address. If CSB is kept high long enough the pre-driver will be able to complete the write instruction.

In total three verification steps are possible in order to ensure successful writing of the EEPROM. On the first MISO-frame after the write command, it can be checked if the write command is received correctly and the correct address and data are used. In the next two MISO-frames the data written in EEPROM can be read in order to guarantee the desired data has been written in EEPROM

- Verification Step 1: Correct receive of the write instruction using the MISO(N+1)-frame
  - COMM\_ERR = 0 : no communication error detected on MOSI(N)-write command
  - EE\_READY = 1 : the write delay was long enough to finish the write instruction
  - MISO\_PAR = correct : the MISO(N+1)-frame has a correct odd parity bit
  - MISO\_DATA(N+1) = MOSI\_DATA(N) : the correct data was used for the write instruction
  
- Verification Step2: EE\_RDAW1 using the MISO(N+2)-frame
  - COMM\_ERR = 0 : no communication error detected on MOSI(N+2)-RDAW1 command
  - EE\_READY = 1 : the read delay was long enough to finish the read instruction
  - MISO\_PAR = correct : the MISO(N+2)-frame has a correct odd parity bit
  - MISO\_DATA(N+2) = MOSI\_DATA(N) : the correct data is written
  
- Verification Step3: EE\_RDAW2 using the MISO(N+3)-frame
  - COMM\_ERR = 0 : no communication error detected on MOSI(N+3)-RDAW2 command
  - EE\_READY = 1 : the read delay was long enough to finish the read instruction
  - MISO\_PAR = correct : the MISO(N+3)-frame has a correct odd parity bit
  - MISO\_DATA(N+3) = MOSI\_DATA(N) : the correct data is written

## 13. ESD Protection

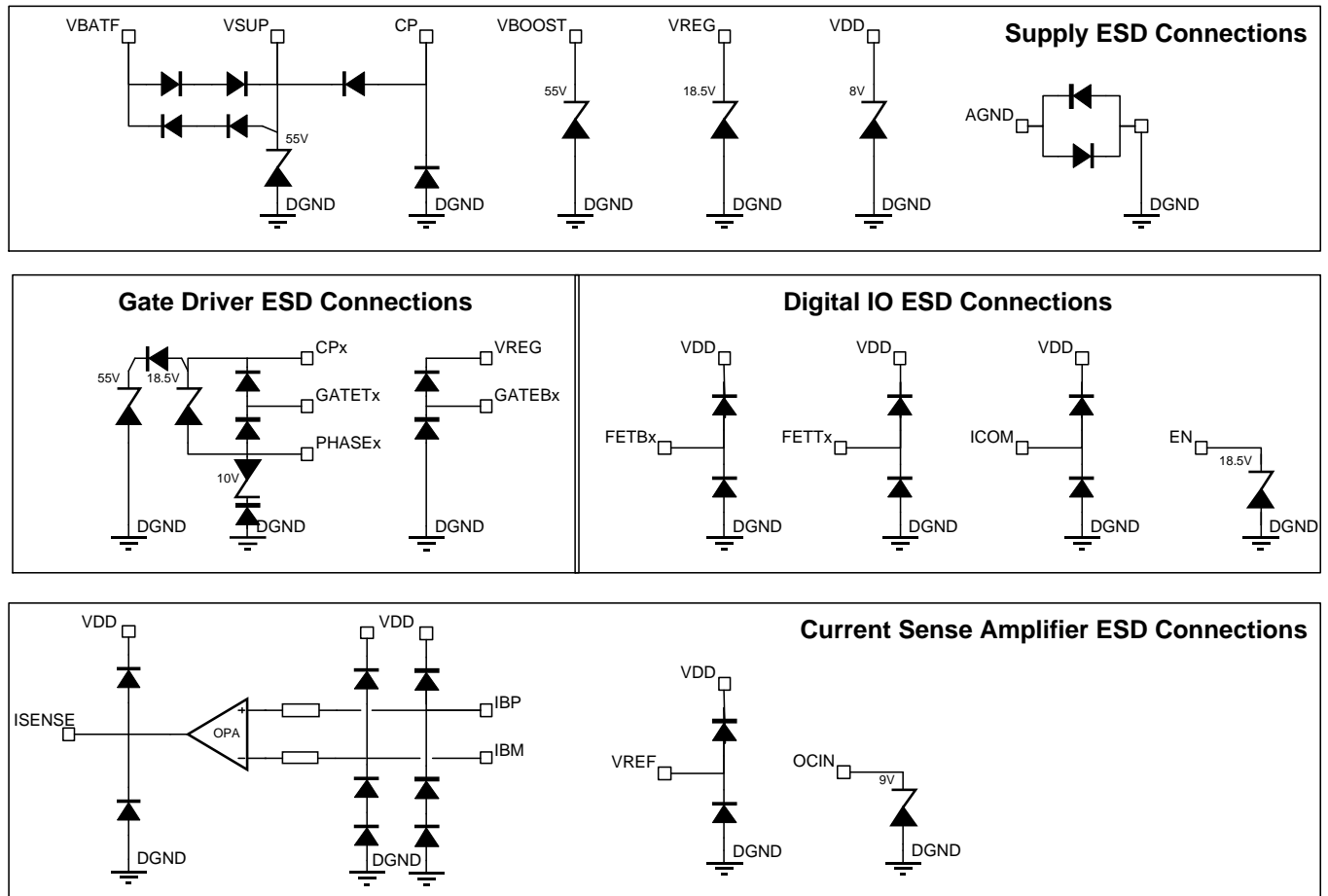


Figure 13-1 Principle Schematic highlighting ESD Connections

**Note:**

All pins are referenced to the driver ground DGND as depicted in the picture above, but only for the ESD protection.

## 14. Package Information

### 14.1. Package Marking

Product name: MLX83203DD or MLX83202DD

Lot number:   xxxxxx           format free

Date code:    yyww           year and week



*Figure 14-1 Package marking*

## 14.2. Package Data

	A	A1	A3	D	E	D2	E2	L	K	b	e
Min.	0.80	0	0.2 REF	4.90	4.90	3.50	3.50	0.30	0.20	0.18	0.50 BSC
Nom.	0.90	0.025		5.00	5.00	3.60	3.60	0.40	-	0.25	
Max.	1.00	0.050		5.10	5.10	3.70	3.70	0.50	-	0.30	

Table 14-1 Mechanical dimensions

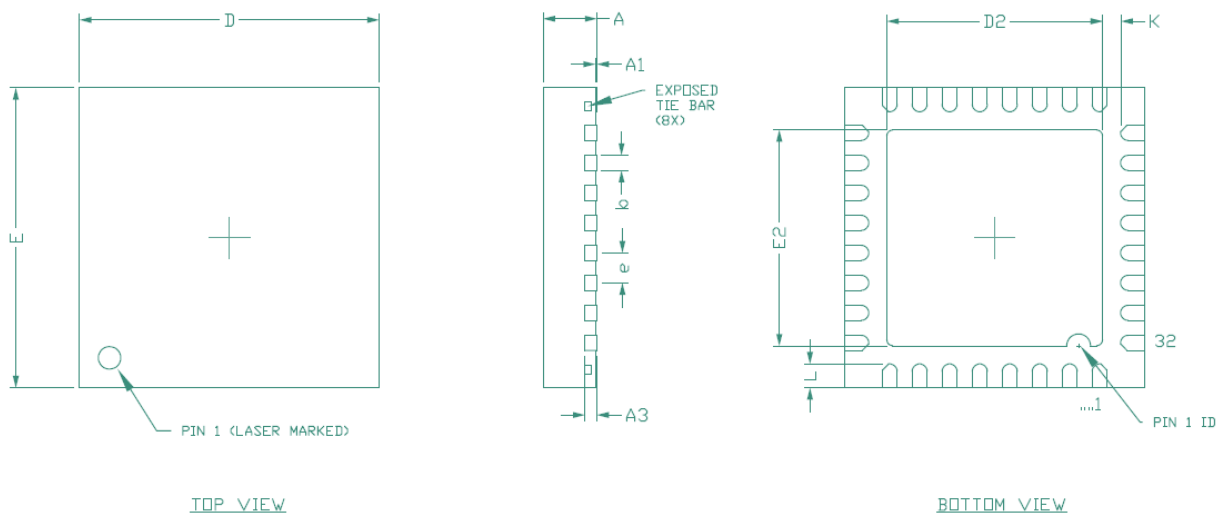


Figure 14-2 Package drawing and mechanical dimensions

## 15. Revision History

Revision	Date	Description
1.0	01-02-12	<ul style="list-style-type: none"> <li>Initial Draft version</li> </ul>
1.1	01-03-12	<ul style="list-style-type: none"> <li>EE_RD meaning in SPI description corrected</li> <li>RDSon specification split up in ON/OFF</li> <li>Added RDSon for 83202 variant</li> <li>Added package marking</li> </ul>
1.2	28-03-12	<ul style="list-style-type: none"> <li>TQFP48 pin out included</li> </ul>
1.3	15-05-12	<ul style="list-style-type: none"> <li>Added appl. Schematics, Pin internal structures, updated block diagram</li> <li>Updated SPI enabling.</li> <li>Updated ICOM duty cycles</li> <li>Updated sleep mode</li> <li>Updated leakage spec on VBATF</li> </ul>
		<ul style="list-style-type: none"> <li>Max voltage on all pins</li> </ul>
1.4	03-07-12	<ul style="list-style-type: none"> <li>Final package dimensions</li> </ul>
1.5	28-11-12	<ul style="list-style-type: none"> <li>Parameters updated per test data</li> <li>Device description updated</li> </ul>
1.6	21-12-12	<ul style="list-style-type: none"> <li>Information about DC variant of pre-driver moved to separate datasheet</li> </ul>
1.7	15-01-13	<ul style="list-style-type: none"> <li>Protection and diagnostic functions updated</li> </ul>
2.0	26-02-13	<ul style="list-style-type: none"> <li>Customer release</li> </ul>
2.1	06-05-13	<ul style="list-style-type: none"> <li>Max voltage on phase pins updated</li> </ul>
2.2	04-12-13	<ul style="list-style-type: none"> <li>Entering SPI mode by disabling all 6x FET input signals</li> </ul>
2.3	01-03-14	<ul style="list-style-type: none"> <li>Temperature codes for ordering information updated</li> <li>Abs. max. rating updated</li> <li>Driver stage specification for 83202 variant added</li> <li>Block diagram and application diagrams updated</li> <li>Changed ICOM duty cycle for VDS_ERR from 5.5% to 82.5%</li> </ul>
3.0	09-05-14	<ul style="list-style-type: none"> <li>General update according to new template</li> </ul>
3.1	24-07-14	<ul style="list-style-type: none"> <li>Drain-source monitor blanking</li> <li>Largest dead time value</li> <li>ICOM pull-up current</li> </ul>
4.0	31-07-14	<ul style="list-style-type: none"> <li>Performance graphs added</li> </ul>
4.1	02-11-15	<ul style="list-style-type: none"> <li>TQFP version cancelled</li> </ul>



## Datasheet

4.2	18-12-15	<ul style="list-style-type: none"> <li>▪ Electrical specifications updated                             <ul style="list-style-type: none"> <li>▪ Operating current from <math>V_{SUP}</math> (with PWM operation)</li> <li>▪ <math>V_{SUP}</math> under and over voltage hysteresis</li> <li>▪ Internal leakage from <math>V_{BATF}</math> to GND</li> <li>▪ <math>V_{DD}</math> operating current</li> <li>▪ Drivers resistance for MLX83202</li> <li>▪ Discharge currents for <math>V_{BOOST}</math> and <math>V_{CPx}</math> specified in case of <math>V_{SUP\_OVH}</math></li> </ul> </li> <li>▪ Ordering information is updated</li> <li>▪ Package information updated</li> </ul>
4.3	17-03-16	<ul style="list-style-type: none"> <li>▪ “Data in hold time” and “Data out ready delay” units corrected to ns</li> </ul>
4.4	31-08-16	<ul style="list-style-type: none"> <li>▪ Default EEPROM configuration corrected for PWM_SPEED</li> <li>▪ Minimum specification on input PWM frequency removed</li> <li>▪ Drain-source voltage monitoring description updated with pin-description</li> </ul>
5.0	01-09-16	<ul style="list-style-type: none"> <li>▪ New Melexis template</li> </ul>
5.1	13-12-16	<ul style="list-style-type: none"> <li>▪ No reduced gate drive voltage for higher extended supply range</li> </ul>
5.2	28-06-17	<ul style="list-style-type: none"> <li>▪ Package marking updated</li> </ul>
5.4	13-03-19	<ul style="list-style-type: none"> <li>▪ Order code and package marking updated for DCA-version</li> <li>▪ ICOM Duty cycles corrected, added duty cycle accuracy</li> <li>▪ Entry in SPI mode after POR specified</li> <li>▪ TCP Removed</li> <li>▪ Package dimensions updated</li> </ul>
5.6	26-06-19	<ul style="list-style-type: none"> <li>▪ “General Electrical Specifications”: <math>VDS\_BLANK\_TIME</math> options reversed</li> </ul>
5.7	11-06-20	<ul style="list-style-type: none"> <li>▪ “Entering SPI Program Mode” updated including MISO-pin note</li> <li>▪ “General Electrical Specifications”: MISO push-pull stage specification</li> </ul>
5.8	15-12-20	<ul style="list-style-type: none"> <li>▪ Order code and package marking updated for DDA-version</li> <li>▪ TCP Description updated</li> </ul>
5.9	13-04-21	<ul style="list-style-type: none"> <li>▪ TCP performance graph included</li> <li>▪ Max. <math>V_{BATF}</math>-<math>V_{SUP}</math> voltage specified for IC versions before DDA</li> </ul>

*Table 15-1 Revision history*

## 16. Standard Information

Our products are classified and qualified regarding soldering technology, solderability and moisture sensitivity level according to standards in place in Semiconductor industry.

For further details about test method references and for compliance verification of selected soldering method for product integration, Melexis recommends reviewing on our web site the [General Guidelines soldering recommendation](#). For all soldering technologies deviating from the one mentioned in above document (regarding peak temperature, temperature gradient, temperature profile etc), additional classification and qualification tests have to be agreed upon with Melexis.

For package technology embedding trim and form post-delivery capability, Melexis recommends to consult the dedicated trim&form recommendation application note: [lead trimming and forming recommendations](#)

Melexis is contributing to global environmental conservation by promoting lead free solutions. For more information on qualifications of RoHS compliant products (RoHS = European directive on the Restriction Of the use of certain Hazardous Substances) please visit the quality page on our website: <http://www.melexis.com/en/quality-environment>

## 17. ESD Precautions

Electronic semiconductor products are sensitive to Electro Static Discharge (ESD).

Always observe Electro Static Discharge control procedures whenever handling semiconductor products.

## 18. Contact

For additional information, please contact our Direct Sales team and get help for your specific needs:

Europe, Africa	Telephone: +32 13 67 04 95
	Email : sales_europe@melexis.com
Americas	Telephone: +1 603 223 2362
	Email : sales_usa@melexis.com
Asia	Email : sales_asia@melexis.com

## 19. Disclaimer

*The content of this document is believed to be correct and accurate. However, the content of this document is furnished "as is" for informational use only and no representation, nor warranty is provided by Melexis about its accuracy, nor about the results of its implementation. Melexis assumes no responsibility or liability for any errors or inaccuracies that may appear in this document. Customer will follow the practices contained in this document under its sole responsibility. This documentation is in fact provided without warranty, term, or condition of any kind, either implied or expressed, including but not limited to warranties of merchantability, satisfactory quality, non-infringement, and fitness for purpose. Melexis, its employees and agents and its affiliates' and their employees and agents will not be responsible for any loss, however arising, from the use of, or reliance on this document. Notwithstanding the foregoing, contractual obligations expressly undertaken in writing by Melexis prevail over this disclaimer.*

*This document is subject to change without notice, and should not be construed as a commitment by Melexis. Therefore, before placing orders or prior to designing the product into a system, users or any third party should obtain the latest version of the relevant information.*

*Users or any third party must determine the suitability of the product described in this document for its application, including the level of reliability required and determine whether it is fit for a particular purpose.*

*This document as well as the product here described may be subject to export control regulations. Be aware that export might require a prior authorization from competent authorities. The product is not designed, authorized or warranted to be suitable in applications requiring extended temperature range and/or unusual environmental requirements. High reliability applications, such as medical life-support or life-sustaining equipment or avionics application are specifically excluded by Melexis. The product may not be used for the following applications subject to export control regulations: the development, production, processing, operation, maintenance, storage, recognition or proliferation of:*

- 1. chemical, biological or nuclear weapons, or for the development, production, maintenance or storage of missiles for such weapons;*
- 2. civil firearms, including spare parts or ammunition for such arms;*
- 3. defense related products, or other material for military use or for law enforcement;*
- 4. any applications that, alone or in combination with other goods, substances or organisms could cause serious harm to persons or goods and that can be used as a means of violence in an armed conflict or any similar violent situation.*

*No license nor any other right or interest is granted to any of Melexis' or third party's intellectual property rights.*

*If this document is marked "restricted" or with similar words, or if in any case the content of this document is to be reasonably understood as being confidential, the recipient of this document shall not communicate, nor disclose to any third party, any part of the document without Melexis' express written consent. The recipient shall take all necessary measures to apply and preserve the confidential character of the document. In particular, the recipient shall (i) hold document in confidence with at least the same degree of care by which it maintains the confidentiality of its own proprietary and confidential information, but no less than reasonable care; (ii) restrict the disclosure of the document solely to its employees for the purpose for which this document was received, on a strictly need to know basis and providing that such persons to whom the document is disclosed are bound by confidentiality terms substantially similar to those in this disclaimer; (iii) use the document only in connection with the purpose for which this document was received, and reproduce document only to the extent necessary for such purposes; (iv) not use the document for commercial purposes or to the detriment of Melexis or its customers. The confidentiality obligations set forth in this disclaimer will have indefinite duration and in any case they will be effective for no less than 10 years from the receipt of this document.*

*This disclaimer will be governed by and construed in accordance with Belgian law and any disputes relating to this disclaimer will be subject to the exclusive jurisdiction of the courts of Brussels, Belgium.*

*The invalidity or ineffectiveness of any of the provisions of this disclaimer does not affect the validity or effectiveness of the other provisions. The previous versions of this document are repealed.*

*Melexis © - No part of this document may be reproduced without the prior written consent of Melexis. (2020)*

*IATF 16949 and ISO 14001 Certified*